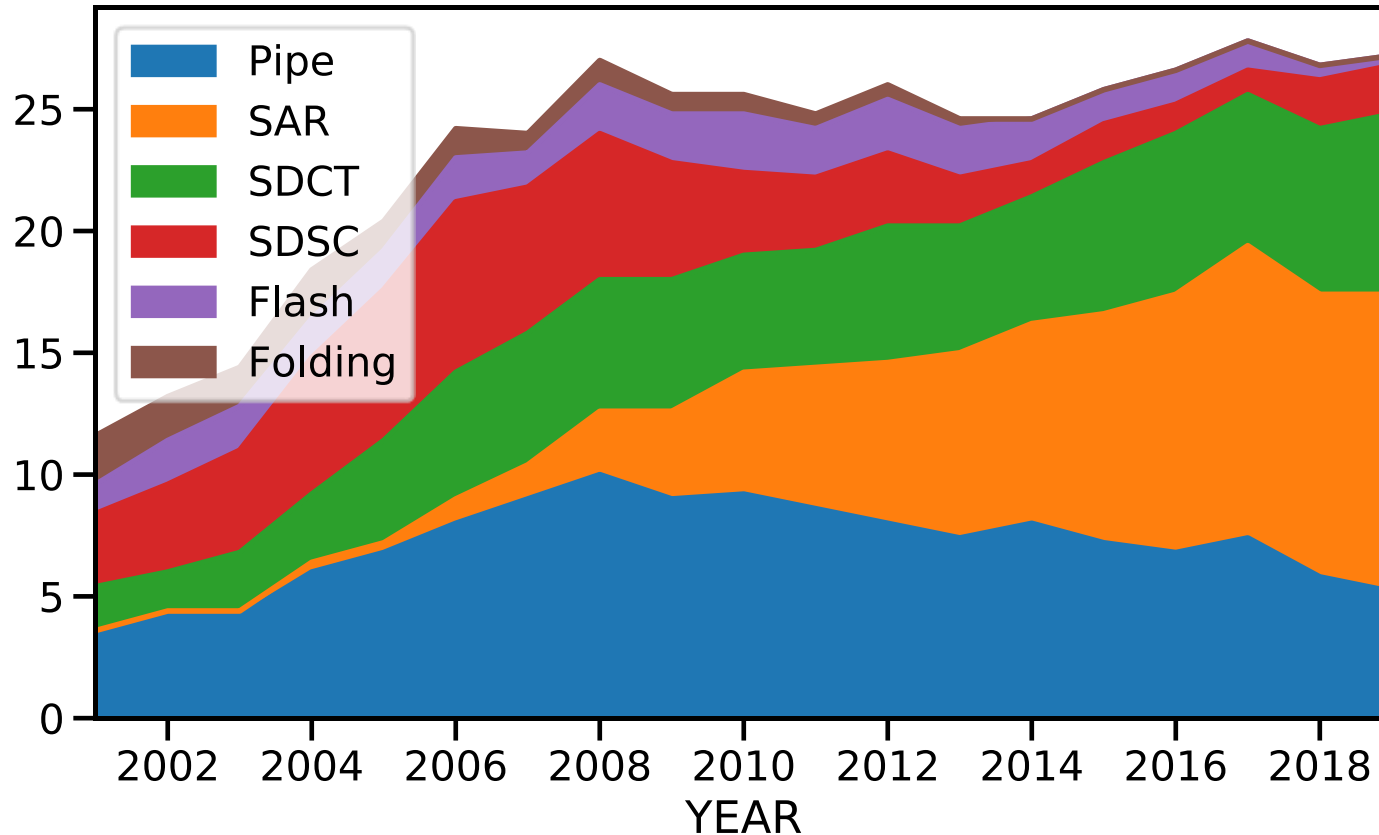


EE 240C

Analog-Digital Interface Integrated Circuits

ADC Architectures

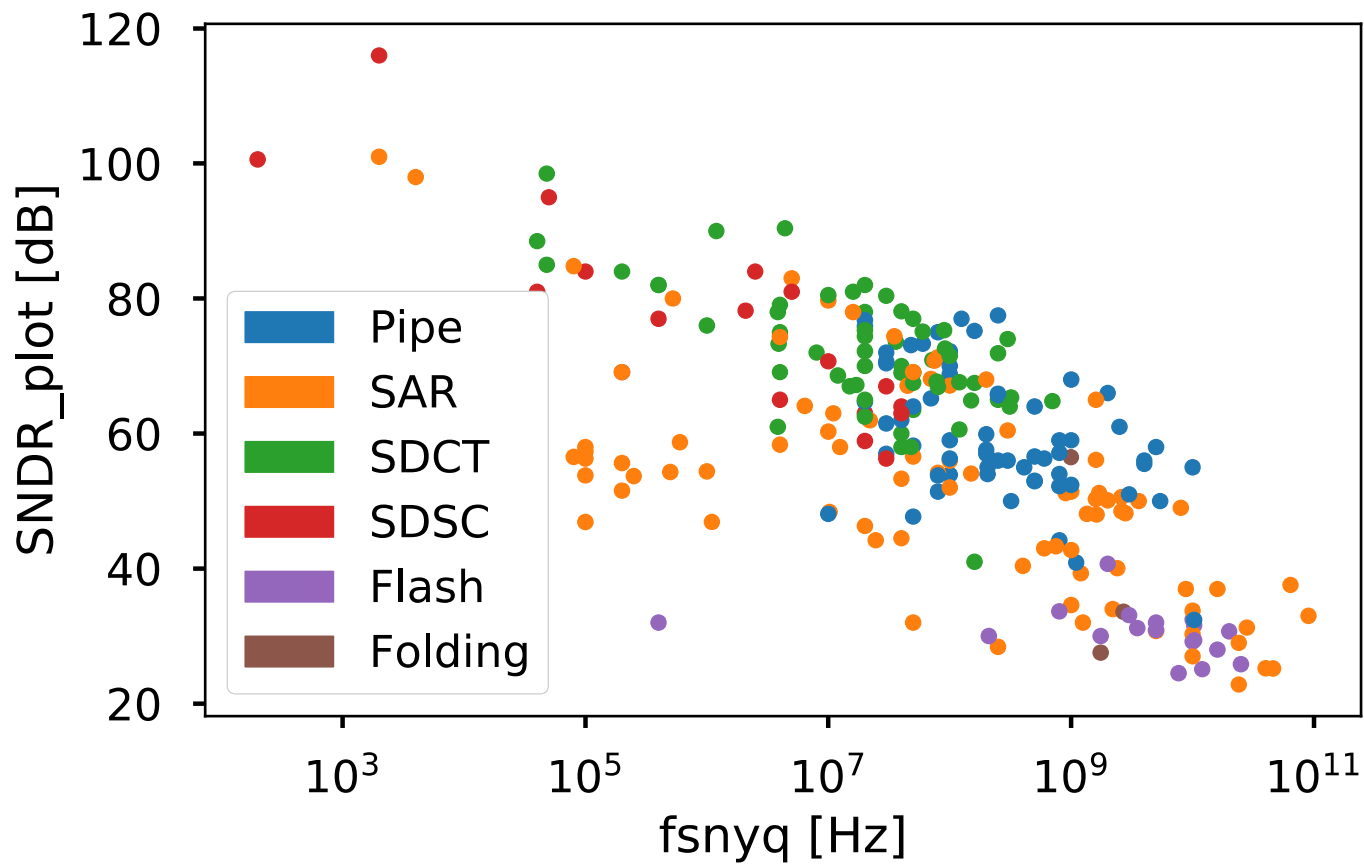
Architectures of Published ADCs (ISSCC and VLSI)



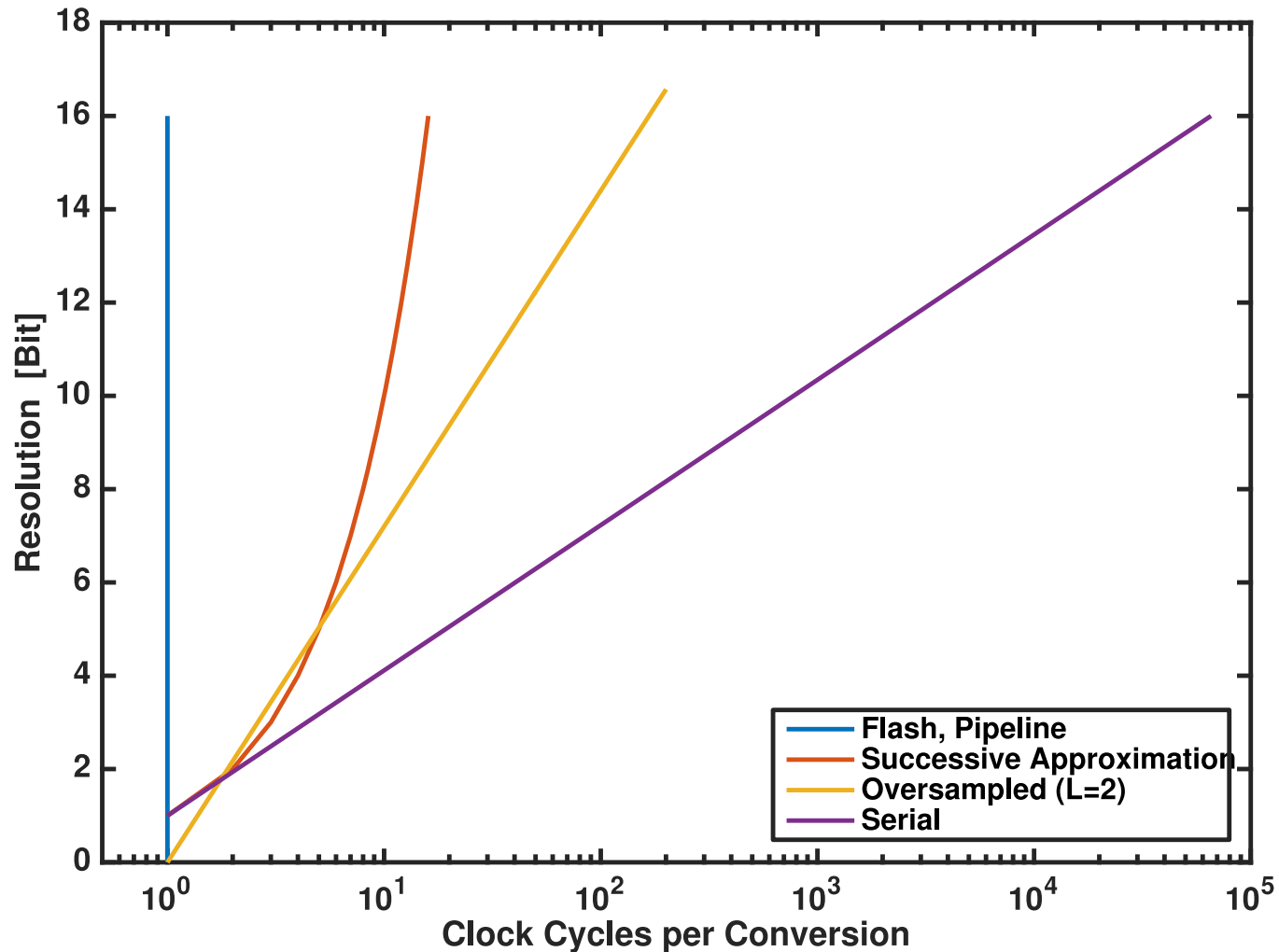
- Evolution due to ADC improvements, technology shift, and focus on low power
- Source data: B. Murmann, "ADC Performance Survey 1997-2019," [Online]. Available: <http://web.stanford.edu/~murmman/adcsurvey.html>
- TI arch. combined with core arch. (e.g. SAR and TI SAR); other arch, (10-15%) not incl.

ADC Performance Survey (ISSCC & VLSI 2007-2017)

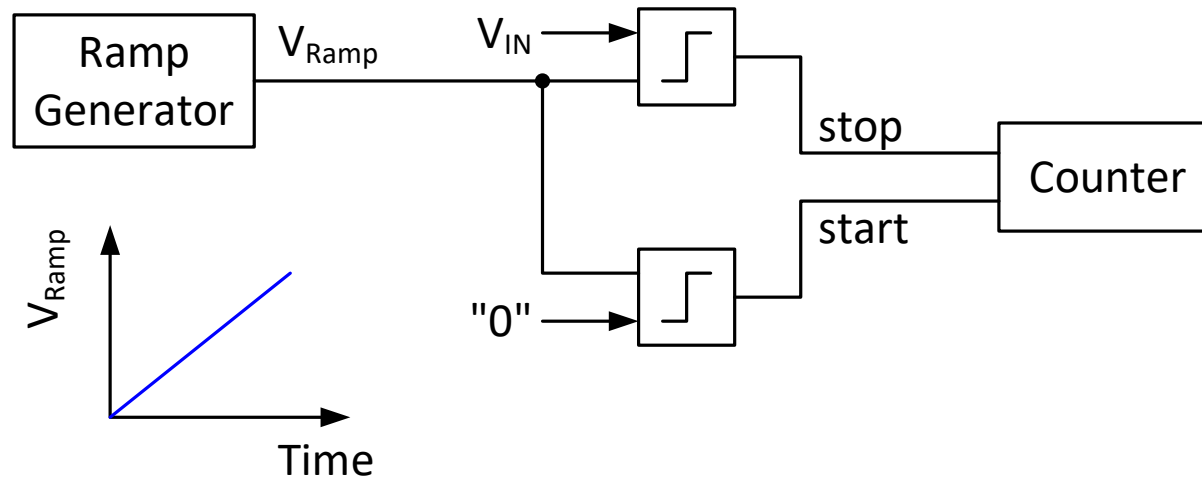
Data: <http://www.stanford.edu/~murmunn/adcsurvey.html>



Speed Comparison

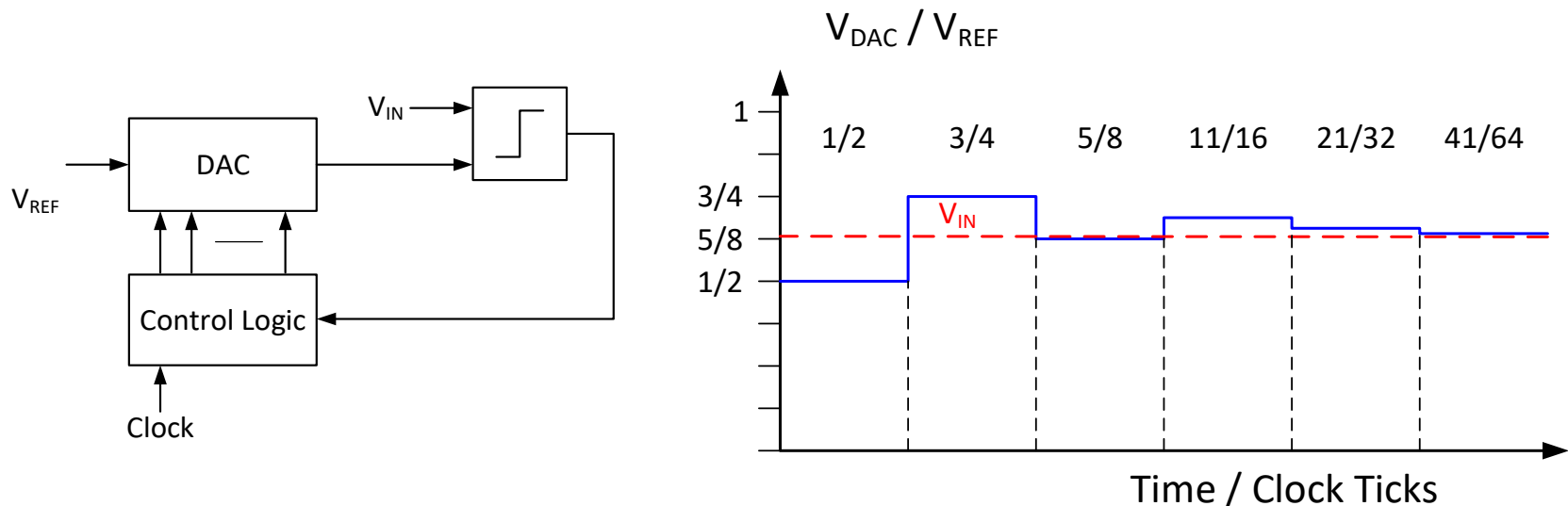


Serial ADC



- Low complexity
- Very high accuracy achievable (digital volt-meter)
- Slow: conversion time proportional 2^B

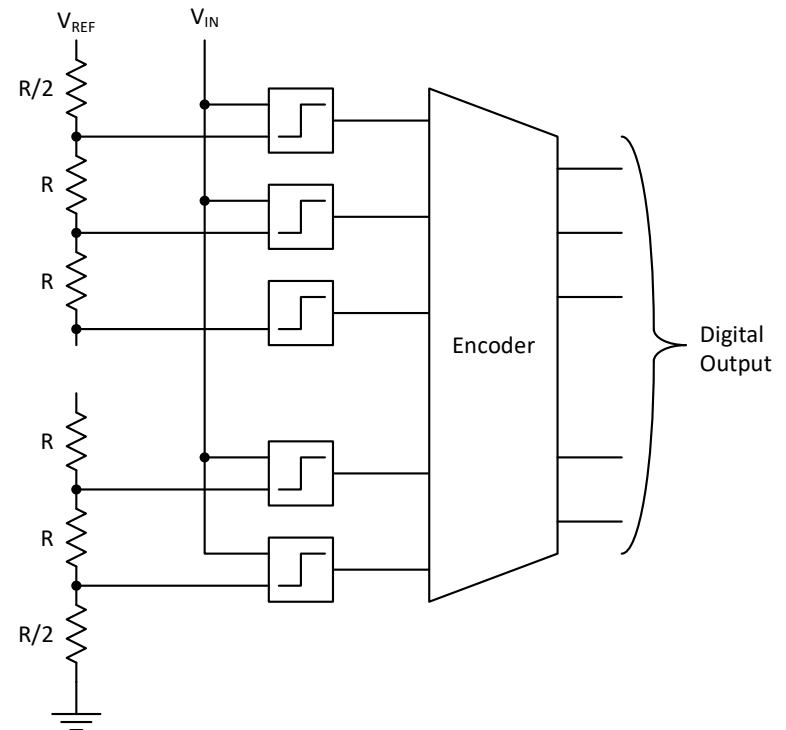
Successive Approximation



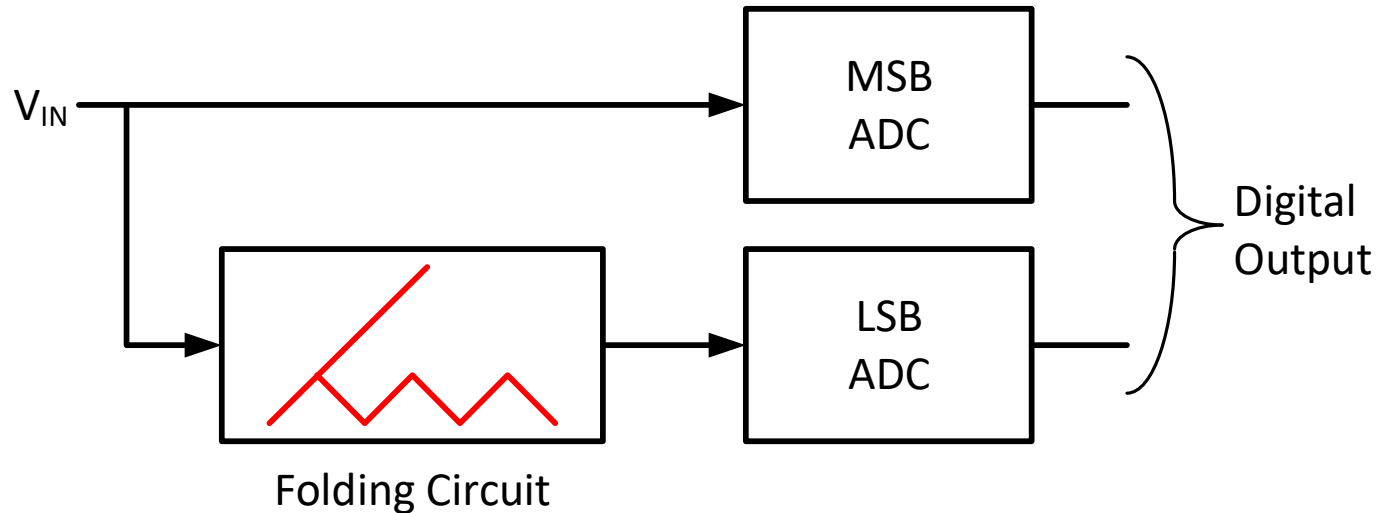
- Binary search over DAC output
- High accuracy achievable (16+ Bits)
- Moderate speed proportional to B (1+ MHz)

Flash Converter

- Very fast: only 1 clock cycle per conversion
- High complexity: $2^B - 1$ comparators
- High input capacitance



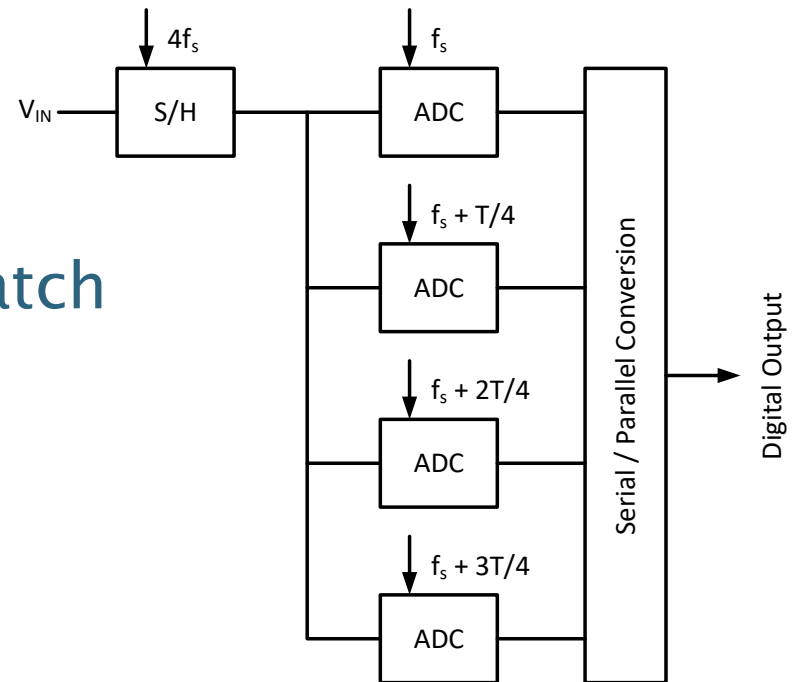
Folding Converter



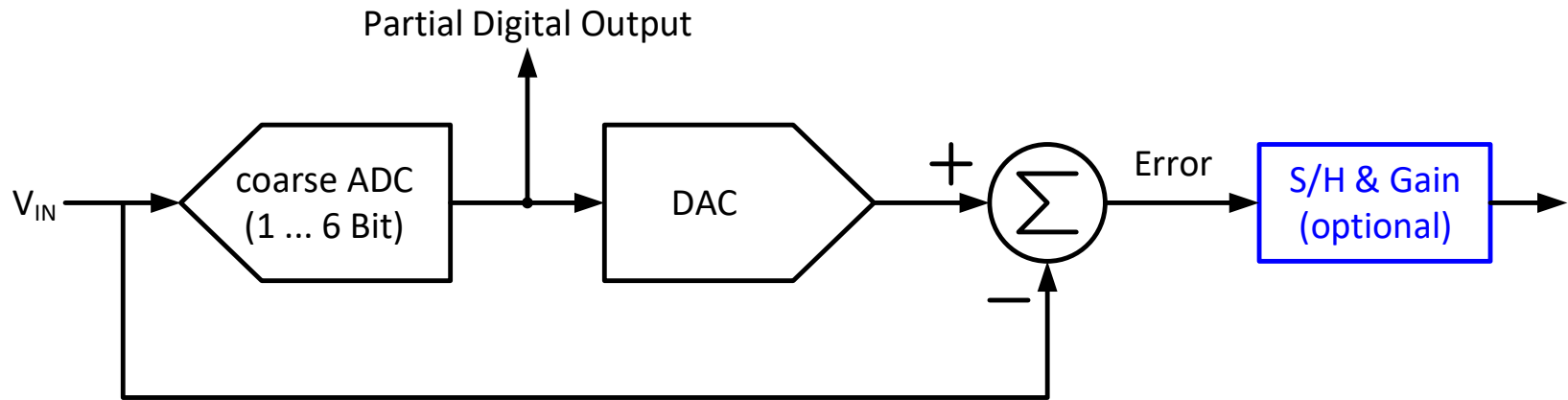
- Significantly fewer comparators than flash $\sim 2^{B/2+1}$
- Fast
- Nonidealities in folder limit resolution to ~ 10 Bits

Time Interleaved Converter

- Extremely fast:
Limited by speed of S/H
- Accuracy limited by mismatch
in individual ADCs
(timing, offset, gain, ...)

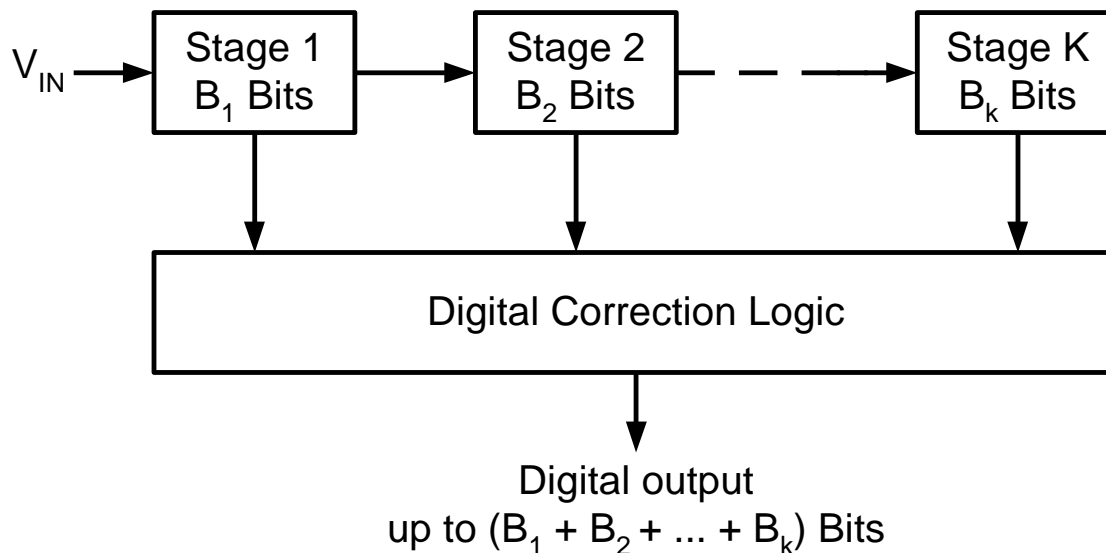


Residue Type ADC



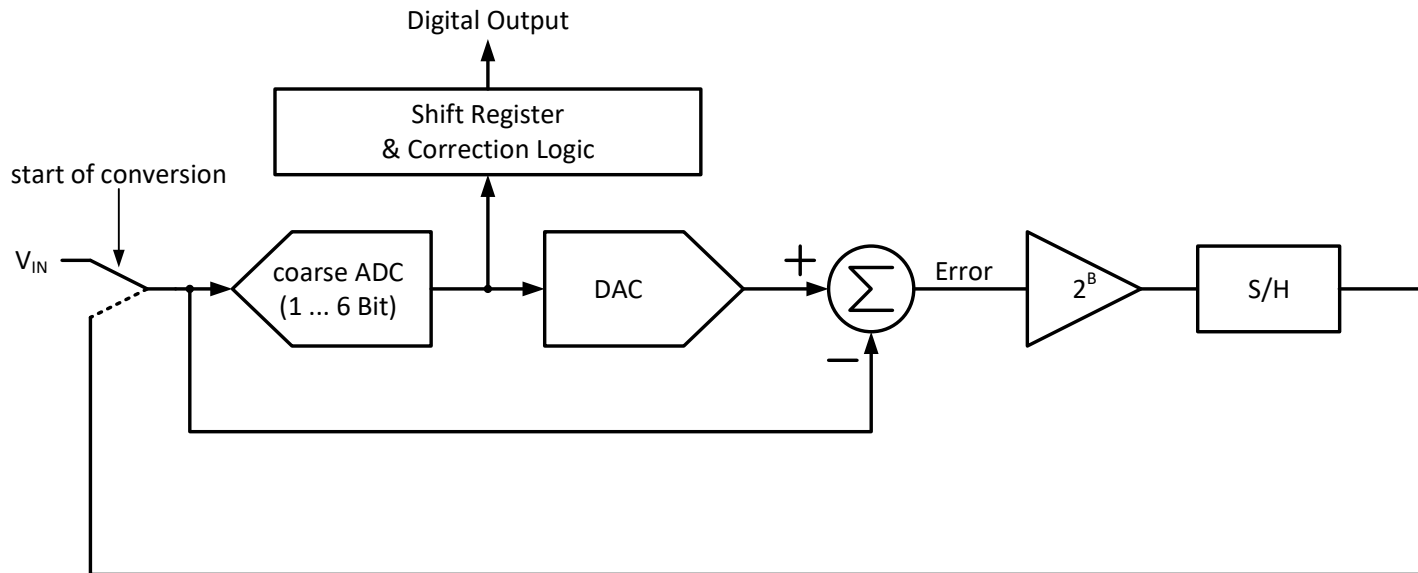
- Quantization error output (“residuum”) enables cascading for higher resolution
- Flexibility for stages: flash, oversampling ADC, ...
- Optional S/H enables parallelism (pipelining)
- Fast: one clock per conversion (with S/H), latency

Pipelined ADC



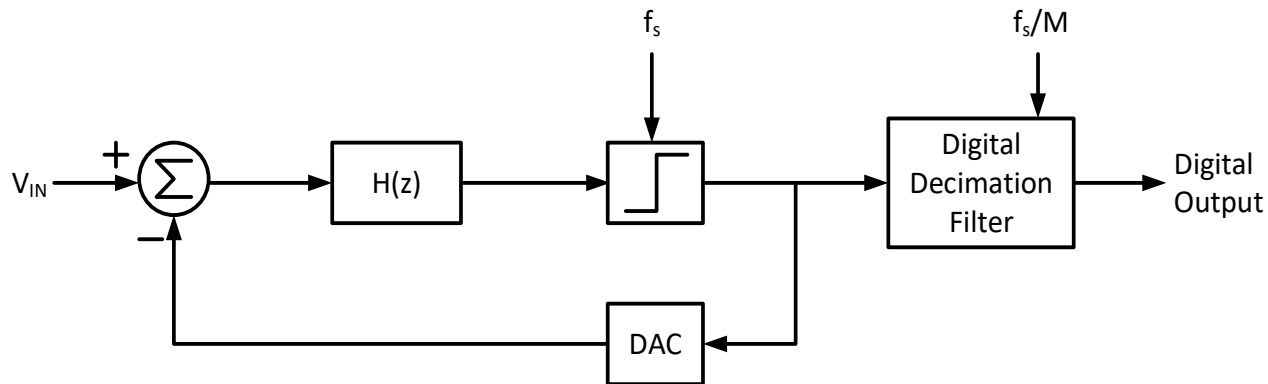
- Approaches speed of flash, but lower complexity
- One clock per conversion, but K clocks latency
- Efficient digital calibration possible
- Versatile: from 16Bits/1MS/s to 14Bits/100MS/s

Algorithmic ADC



- Essentially same as pipeline, but a single stage is used for all partial conversions
- K clocks per conversion

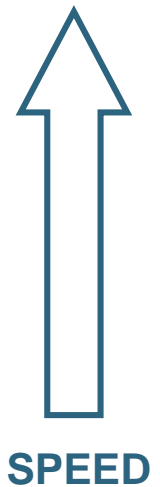
Oversampled ADC



- Hard to comprehend ... “easy” to build
- Input is oversampled (M times output rate)
- Reduces Anti-Aliasing filter requirements and capacitor size
- Accuracy independent of component matching
- Very high resolution achievable (> 20 Bits)

Nyquist ADC Architectures

- Nyquist rate
 - Word-at-a-time
 - Flash ADC
 - Instantaneous comparison with $2^B - 1$ reference levels
 - Multi-step
 - E.g. pipeline ADCs
 - Coarse conversion, followed by fine conversion of residuum
 - Bit-at-a-time
 - E.g. successive approximation ADCs
 - Conversion via a binary search algorithm
 - Level-at-a-time
 - E.g. single or dual slope ADCs
 - Input is converted by measuring the time it takes to charge/discharge a capacitor from/to input voltage



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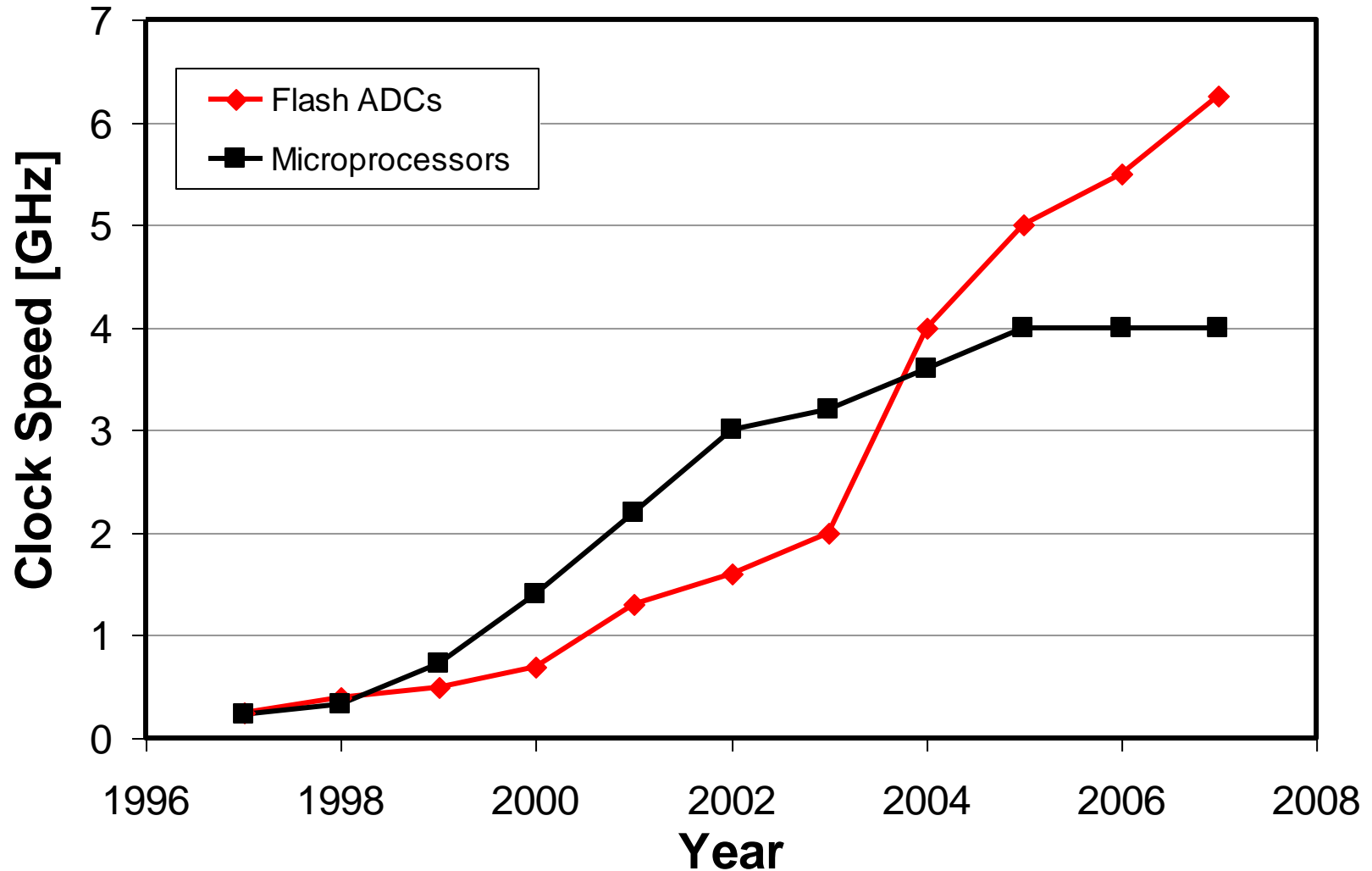
Analog-Digital Interface Integrated Circuits

Flash Converters

High-Speed A/D Converter

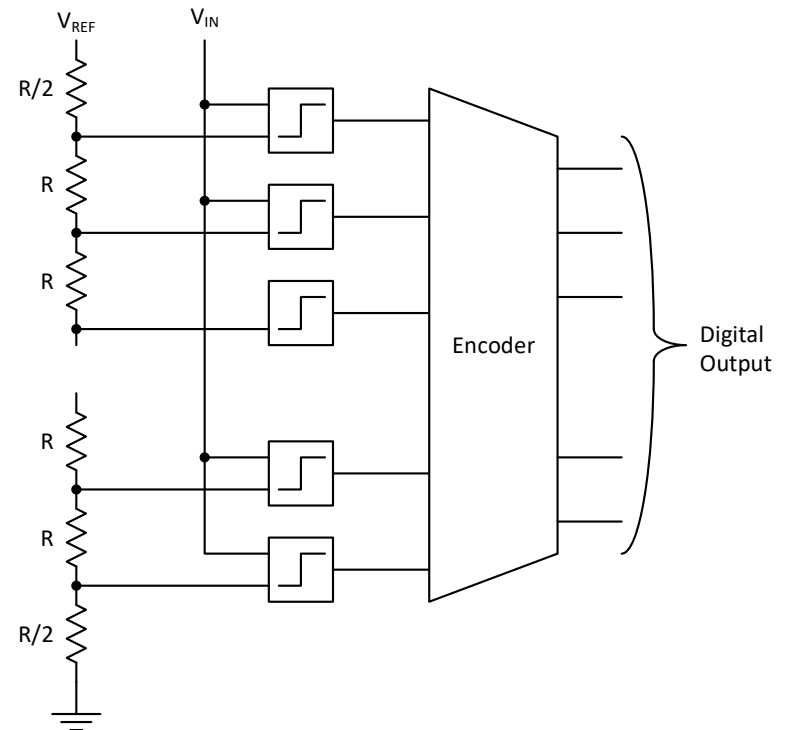
- Flash Converter
 - Comparator
 - Binary Encoder
- Interpolation
- Folding

Flash ADC Speed

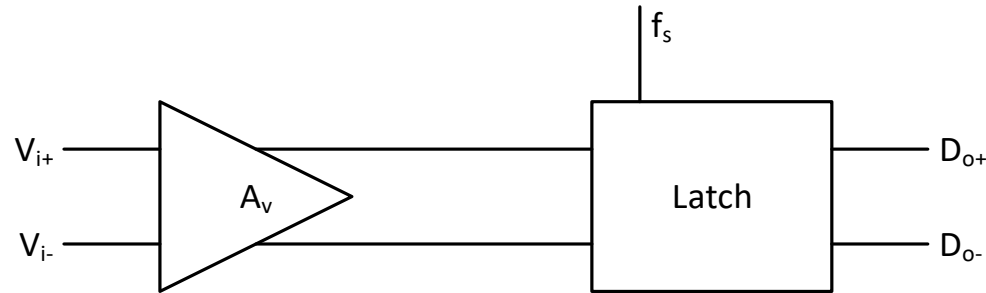


Flash Converter

- Very fast: only 1 clock cycle per conversion
- High complexity: $2^B - 1$ comparators for 2^B levels
- $R/2$ at ends
→ end points $\frac{1}{2}$ LSB beyond end transition
- High input capacitance

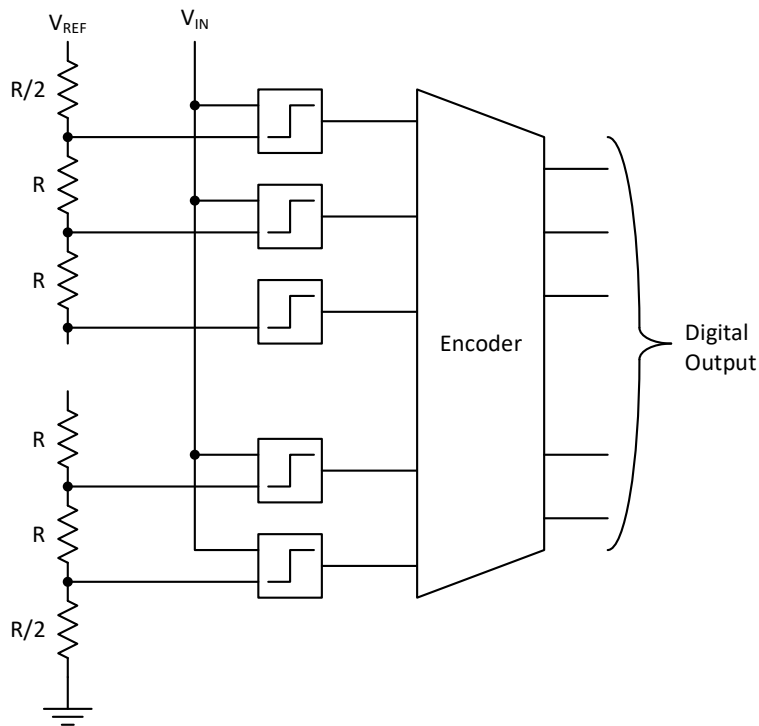


Comparator



- Clock rate f_s
- Resolution
- Overload Recovery
- Input capacitance (and linearity!)
- Power dissipation
- Common-mode rejection
- Kickback noise
- ...

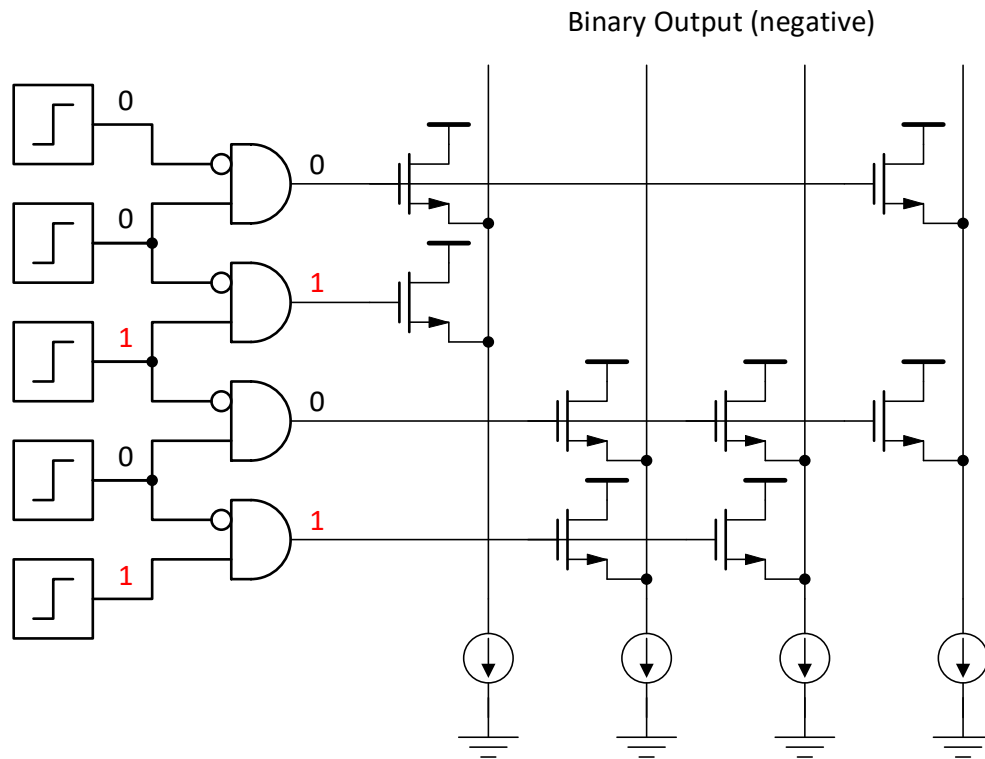
Flash Converter Errors



- Comparator input:
 - Offset
 - Nonlinear input capacitance
 - Kickback noise (disturbs reference)
 - Signal dependent sampling time
- Comparator output:
 - Sparkle codes (...111101000...)
 - Metastability

Ref: Analog Devices application note: "Find Those Elusive ADC Sparkle Codes and Metastable States"
<http://www.analog.com/en/content/0,2886,760%255F788%255F91218,00.html>

Sparkle Codes

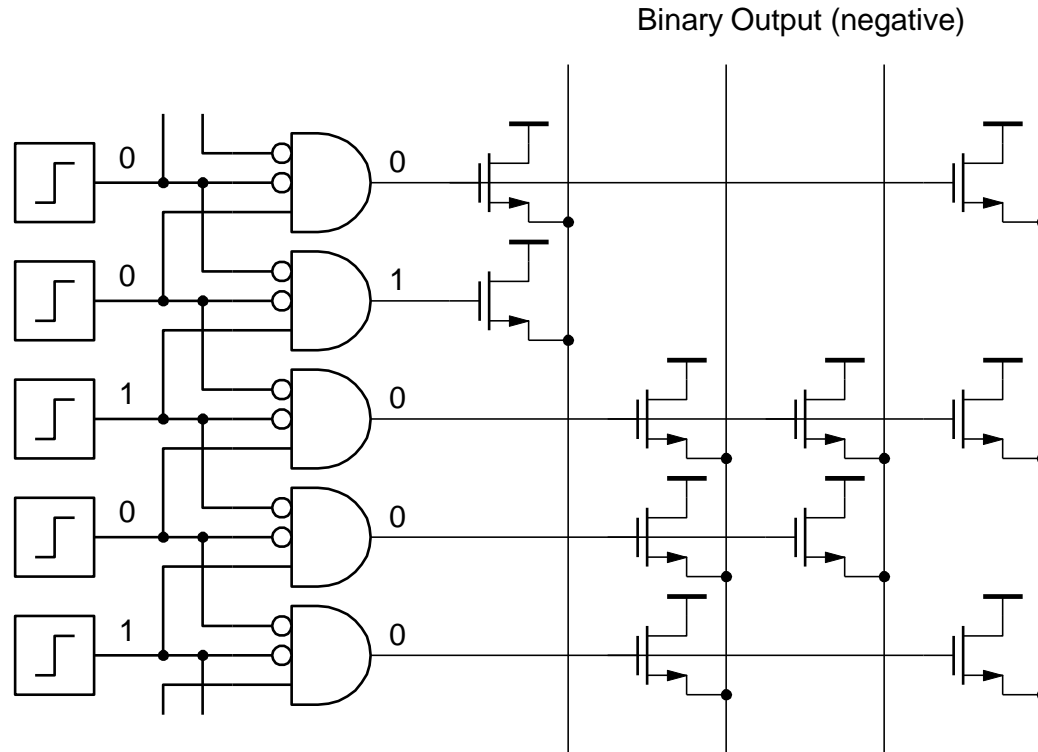


Correct Output:

```
0110 ...
1000
```

Actual Output:
1110

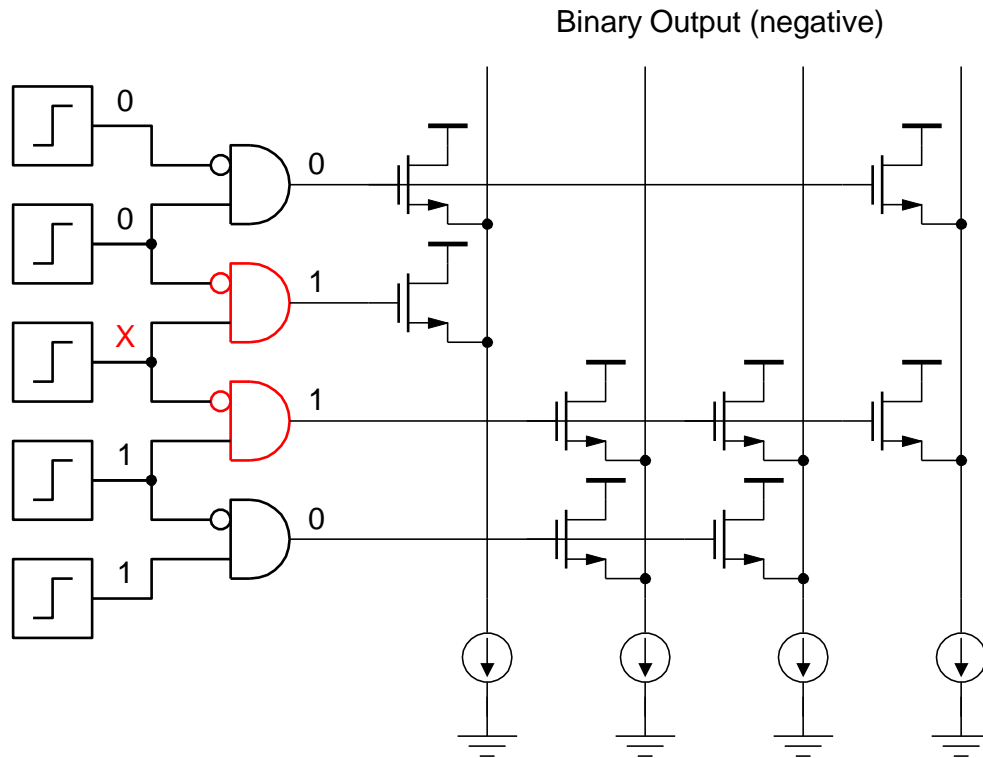
Sparkle Tolerant Encoder



Protects against a *single* sparkle.

Ref: C. Mangelsdorf et al, "A 400-MHz Flash Converter with Error Correction," JSSC February 1990, pp. 997-1002.

Meta Stability



Different gates interpret metastable output X differently

Correct Output: 0111 or 1000

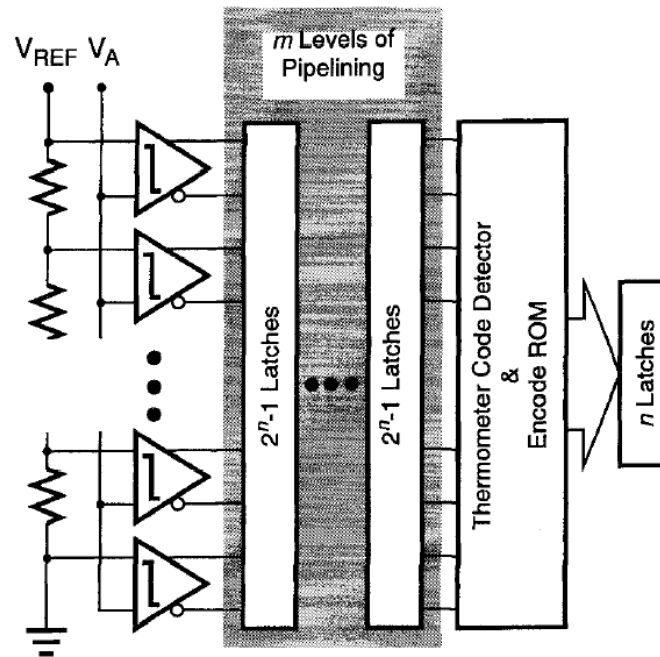
Actual Output: 1111

Solutions:

- Latches (high power)
- Gray encoding
- Adder

Ref: C. Portmann and T. Meng, "Power-Efficient Metastability Error Reduction in CMOS Flash A/D Converters," JSSC August 1996, pp. 1132-40.

Solution 1: Latch Pipelining



- Use additional latches to create extra gain before generating decoder signals
- High power and area inefficient

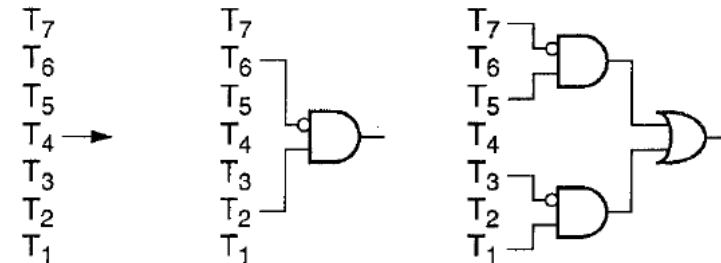
Solution 2: Gray Encoding

Thermometer Code							Gray			Binary		
T ₁	T ₂	T ₃	T ₄	T ₅	T ₆	T ₇	G ₃	G ₂	G ₁	B ₃	B ₂	B ₁
0	0	0	0	0	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	0	0	1	0	0	1
1	1	0	0	0	0	0	0	1	1	0	1	0
1	1	1	0	0	0	0	0	1	0	0	1	1
1	1	1	1	0	0	0	1	1	0	1	0	0
1	1	1	1	1	0	0	1	1	1	1	0	1
1	1	1	1	1	1	0	1	0	1	1	1	0
1	1	1	1	1	1	1	1	0	0	1	1	1

$$G_1 = T_1 \bar{T}_3 + T_5 \bar{T}_7$$

$$G_2 = T_2 \bar{T}_6$$

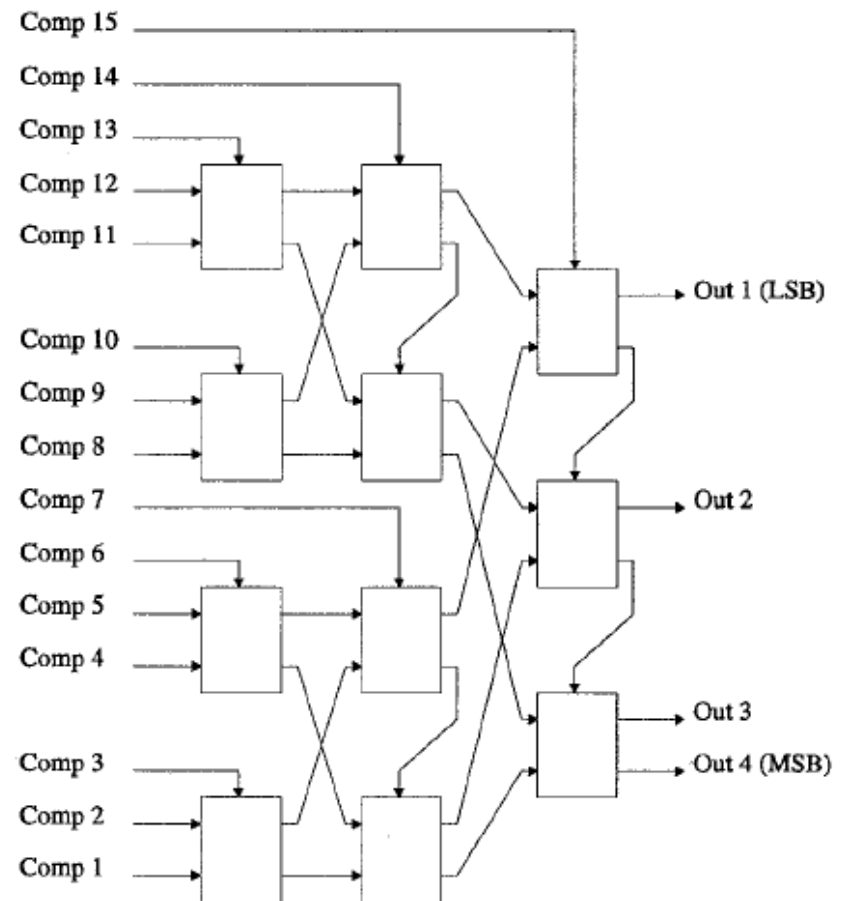
$$G_3 = T_4$$



- Each T_i affects only one G_i
→ Avoids disagreement of interpretation by multiple gates
- Protects also against sparkles
- Follow Gray encoder by (latch and) binary encoder

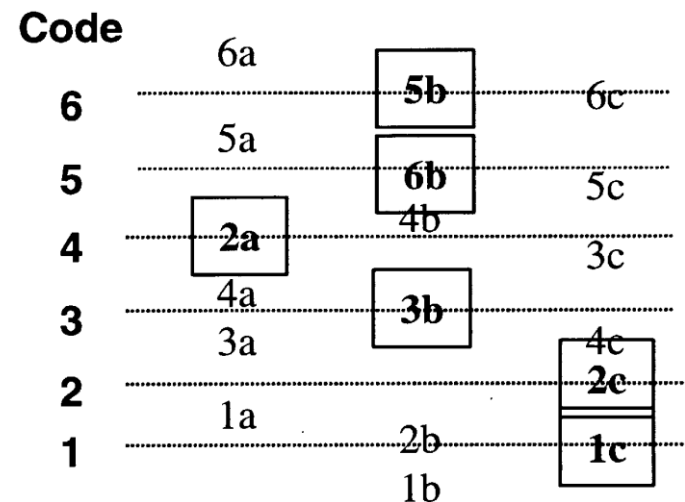
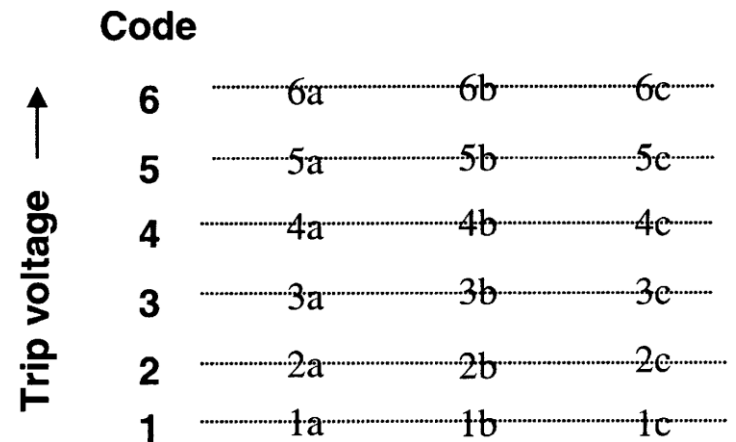
Solution 3: Adder

- Wallace-tree adder
- [F. Kaess et al., “New encoding scheme for high-speed flash ADC’s,” in Proceedings of 1997 IEEE International Symposium on Circuits and Systems, 1997. ISCAS ’97., vol. 1, pp. 5-8 vol.1, June 1997](#)

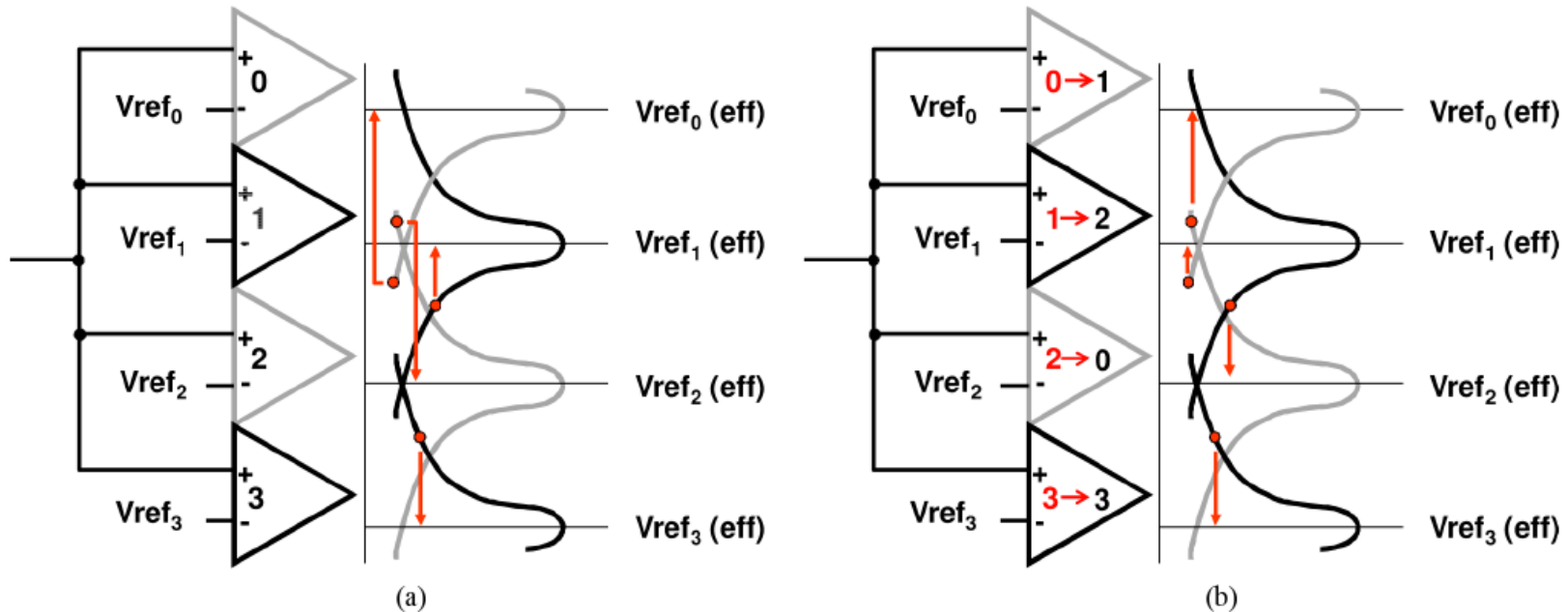


Redundant Comparators

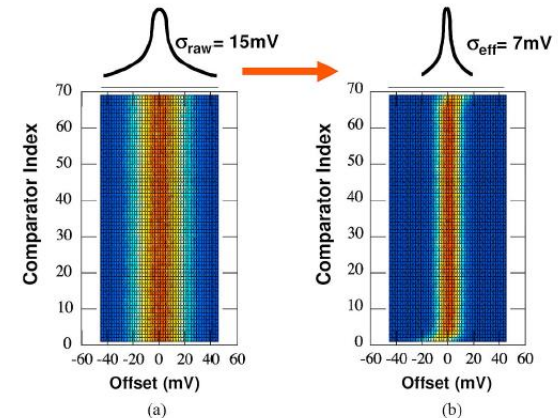
- Redundant comparators
[M. P. Flynn, C. Donovan, and L. Sattler, "Digital calibration incorporating redundancy of flash ADCs," *IEEE J. Solid-State Circuits*, vol. 50, pp. 205-213, May 2003]
- Choose comparators at power-on
- Implementation: select input diff pairs of comparator



Reorder comparators



- [\[A. Varzaghani et al., “A 10.3-GS/s, 6-Bit flash ADC for 10g ethernet applications,” *IEEE J. Solid-State Circu.* vol. 48, pp. 3038–3048, Dec. 2013\]](#)
- Automatically reorder comparators using adder (therm \rightarrow binary)
- Monte Carlo simulations



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Analog-Digital Interface Integrated

Circuits

Interpolation

Offset

- Typically want offset of each comparator $< \frac{1}{4}$ LSB
 - If we budget half of the input referred offset for the latch, the other half for the pre-amp, this means pre-amp offset must be $< \frac{1}{4} \text{ LSB} / \text{sqrt}(2)$

$$3\sigma_{VOS} = 3 \frac{A_{VT}}{\sqrt{WL}} < \frac{1}{4\sqrt{2}} \frac{\text{FSR}}{2^B}$$

- E.g. 6-bit flash ADC, FSR=1V:

$$3 \frac{A_{VT}}{\sqrt{WL}} < \frac{1}{4\sqrt{2}} \frac{1V}{2^6} = 2.8mV$$

$$WL > \left(\frac{3A_{VT}}{2.8mV} \right)^2 = \left(\frac{3 \cdot 4mV\mu m}{2.8mV} \right)^2 = 18.4\mu m^2 \Rightarrow W > \frac{18.4\mu m^2}{0.18\mu m} = 102\mu m$$

Huge!

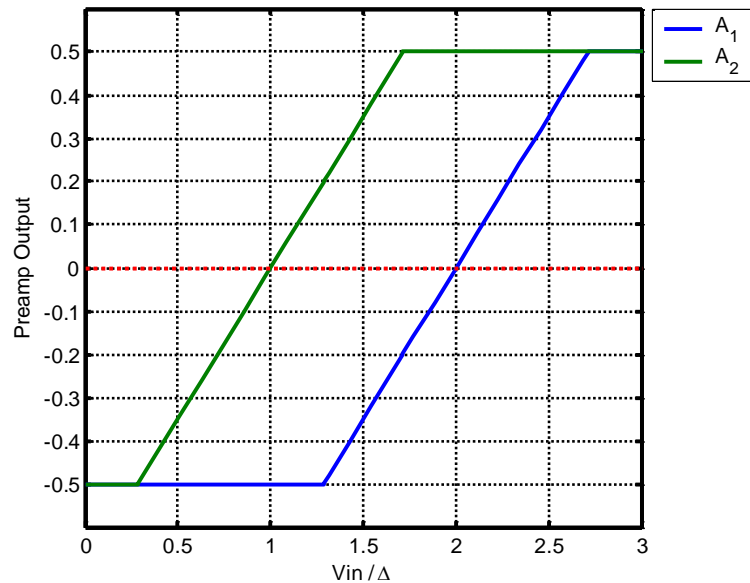
Options

- Simply use large devices
 - For each extra bit, need to increase width by 4x, also need to double number of comparators
 - Assuming constant current density, this means each additional bit costs 8x in power!
- Offset cancellation
 - Tends to cost speed
- Offset averaging
- Calibration and/or postprocessing techniques

Interpolation

- Idea
 - Interpolation between preamp outputs
- Reduces number of preamps
 - Reduced input capacitance
 - Reduced area, power dissipation
- Same number of latches
- Important “side-benefit”
 - Decreased sensitivity to preamp offset
 - → improved DNL

Preamp Output

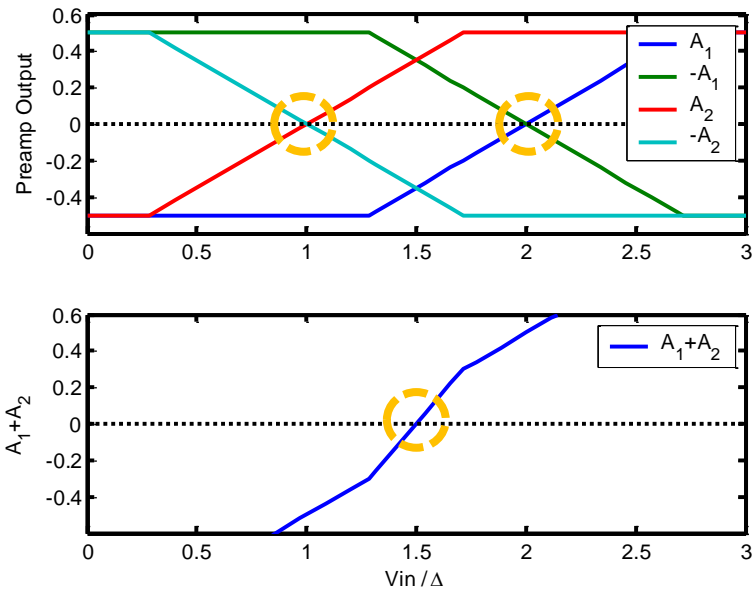


Zero crossings (to be detected by latches) at $V_{in} =$

$$V_{\text{ref1}} = 1 \Delta$$

$$V_{\text{ref2}} = 2 \Delta$$

Differential Preamp Output



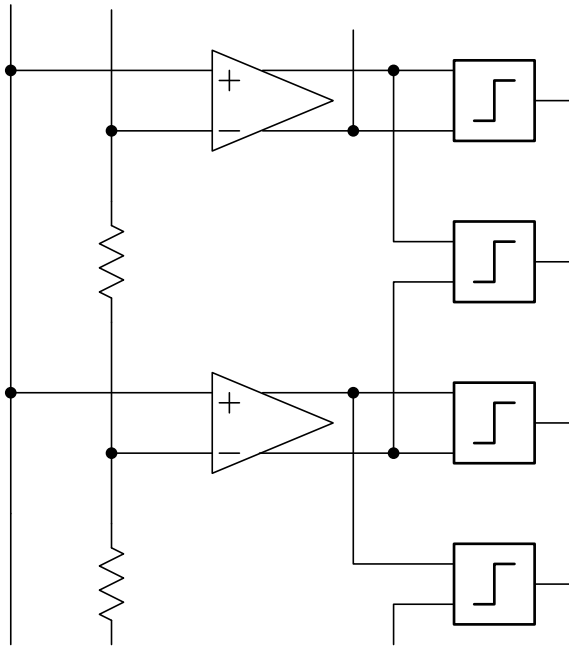
Zero crossings at $V_{in} =$

$$V_{\text{ref1}} = 1 \Delta$$

$$V_{\text{ref12}} = 0.5 \cdot (1+2) \Delta$$

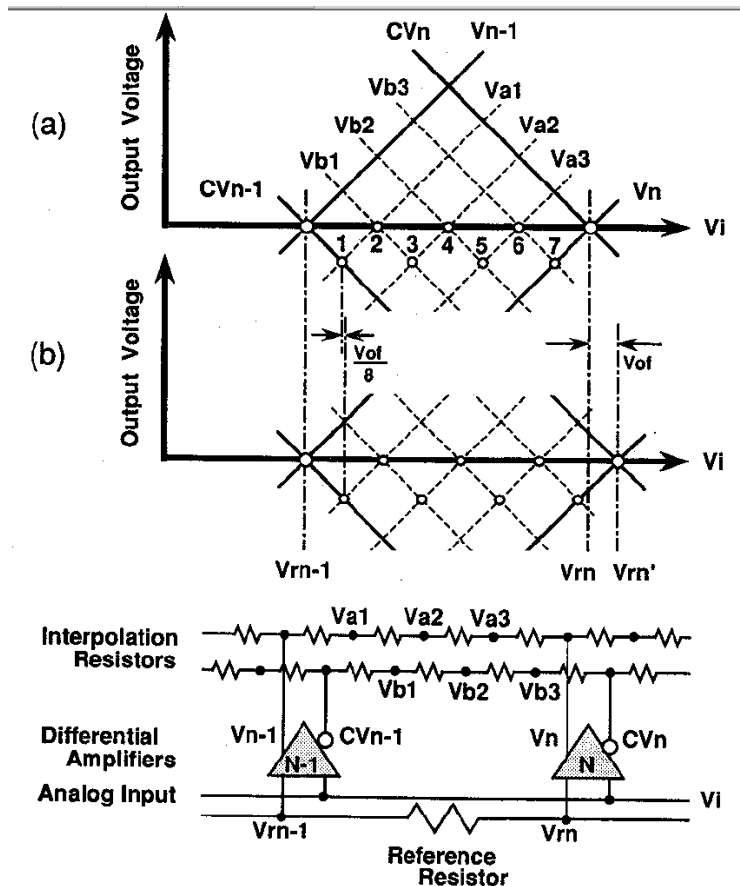
$$V_{\text{ref2}} = 2 \Delta$$

Interpolation in Flash ADC



Half as many reference voltages and preamps

Resistive Interpolation



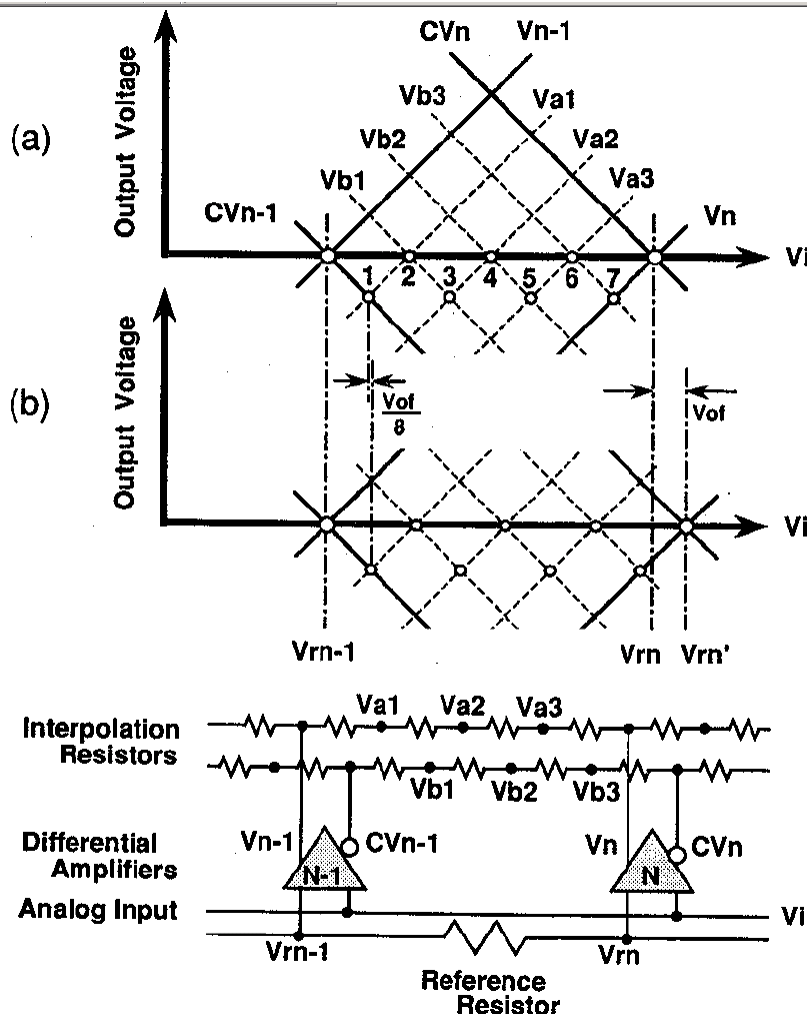
Resistive Interpolation

- Resistors produce additional levels
- Interpolation factor = ratio of latches / preamps
- With 4 resistors, the “interpolation factor” $M=8$

Preamp offset distributed over M resistively interpolated voltages:
 → impact on DNL divided by M

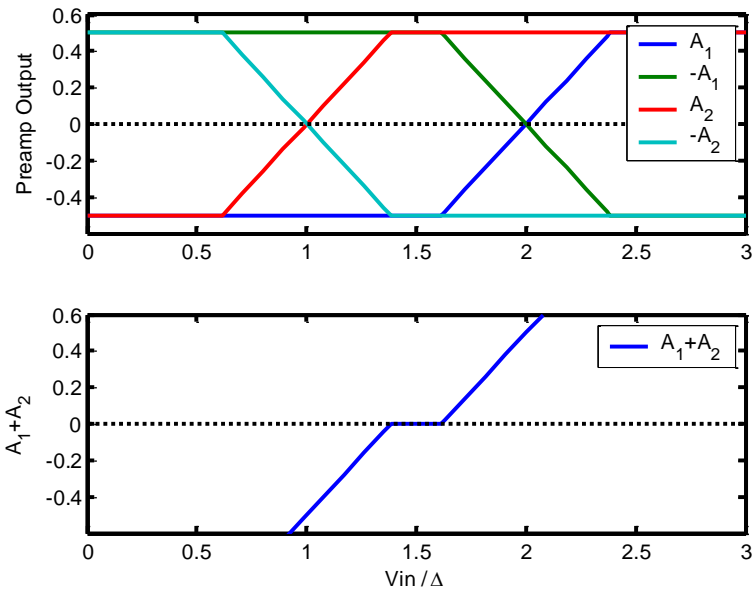
Ref: H. Kimura et al, “A 10-b 300-MHz Interpolated-Parallel A/D Converter,” JSSC April 1993, pp. 438-446.

DNL Improvement



- Preamp offset distributed over M resistively interpolated voltages:
→ impact on DNL divided by M
- Latch offset divided by gain of preamp
→ use “large” preamp gain ...
→ but ...

Preamp Input Range



Linear preamp input ranges must overlap

i.e. $\text{range} > \Delta$

Sets upper bound on gain

$\ll V_{DD} / \Delta$

Example

Resolution		10 b
Maximum conversion frequency		300 MHz
Integral non-linearity		± 1.0 LSB
Differential non-linearity		± 0.4 LSB
SNR/THD	10MHz input	56/-59 dB
	50MHz input	48/-47 dB
Input capacitance		8 pF
Input range		2 V
Power supply		-5.2V
Power dissipation		4.0W
Chip size		$9.0 \times 4.2 \text{ mm}^2$
Element count		36,000
Technology		1.0 μm bipolar:ft=25GHz

Ref: H. Kimura et al, "A 10-b 300-MHz Interpolated-Parallel A/D Converter," JSSC April 1993, pp. 438-446.

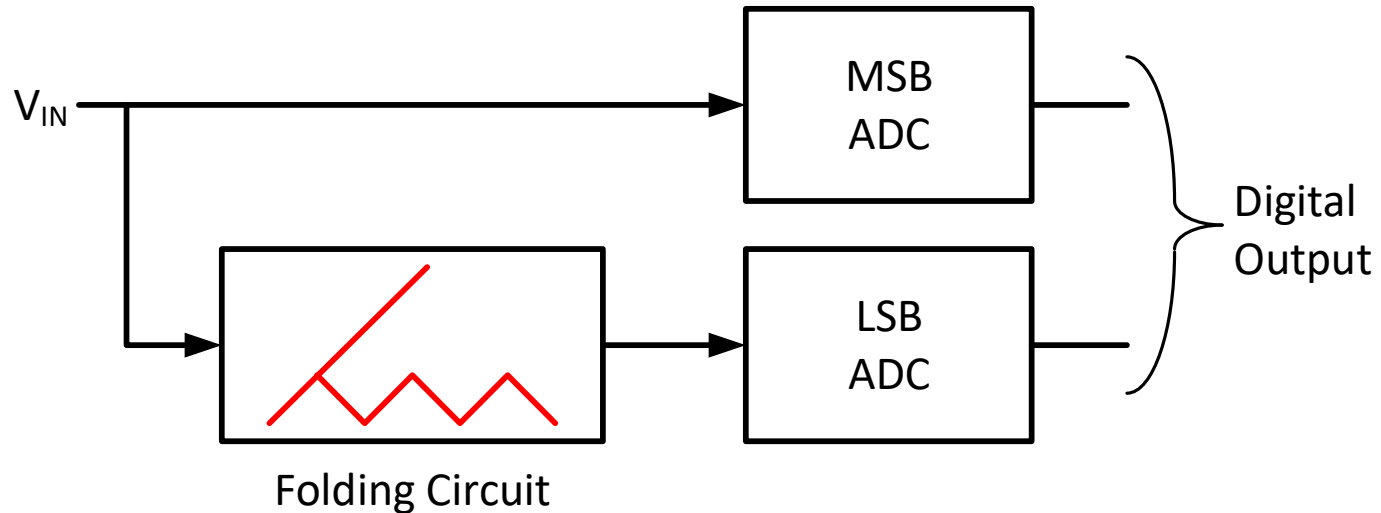
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Analog-Digital Interface Integrated Circuits

Folding ADCs

Folding & Interpolating ADCs

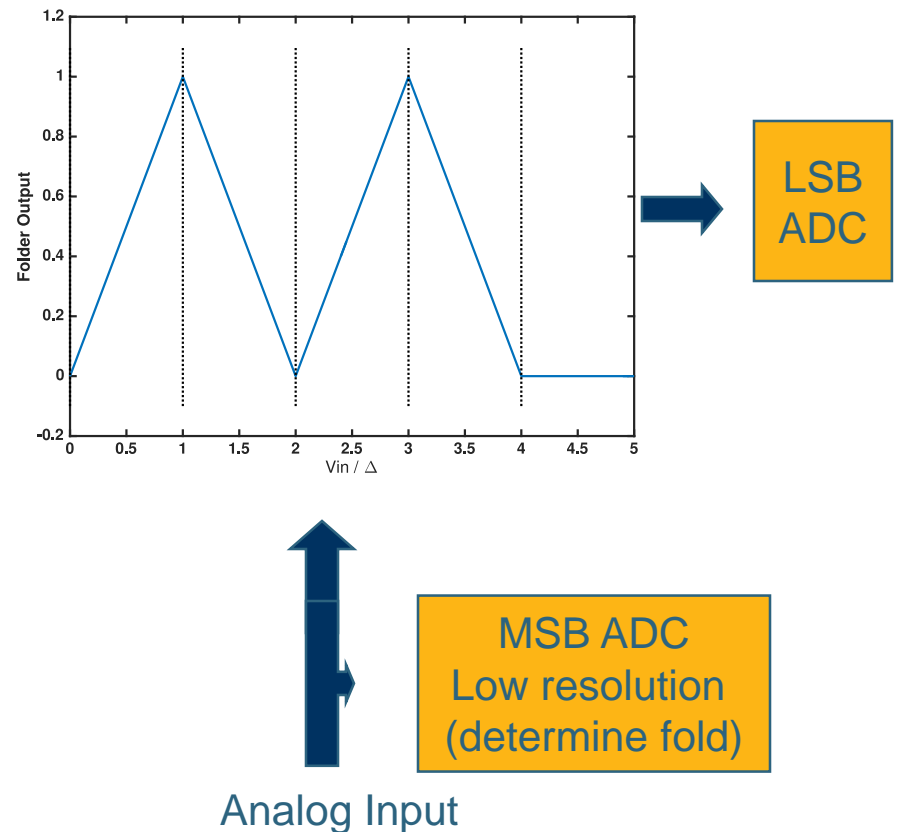
Folding Converter



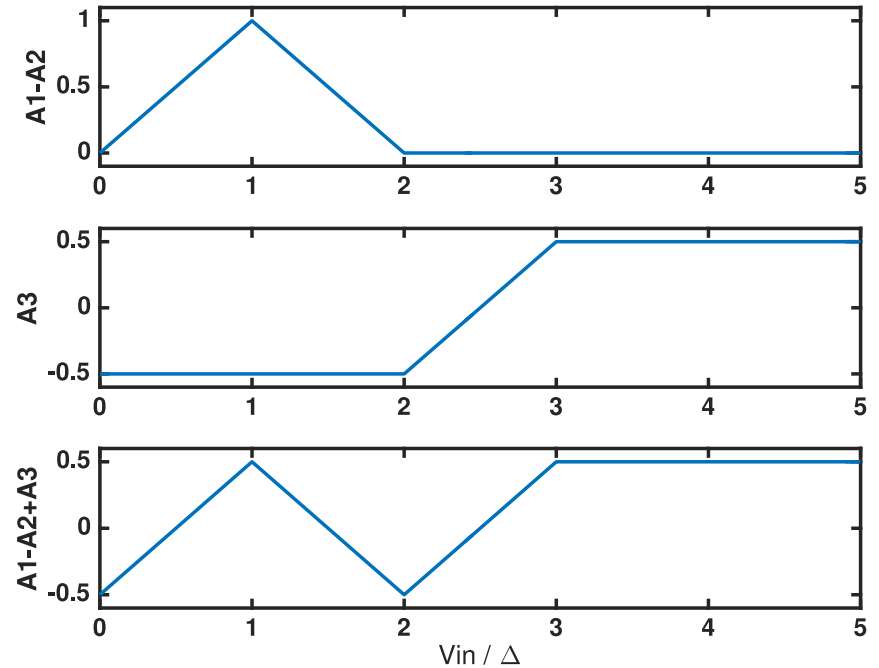
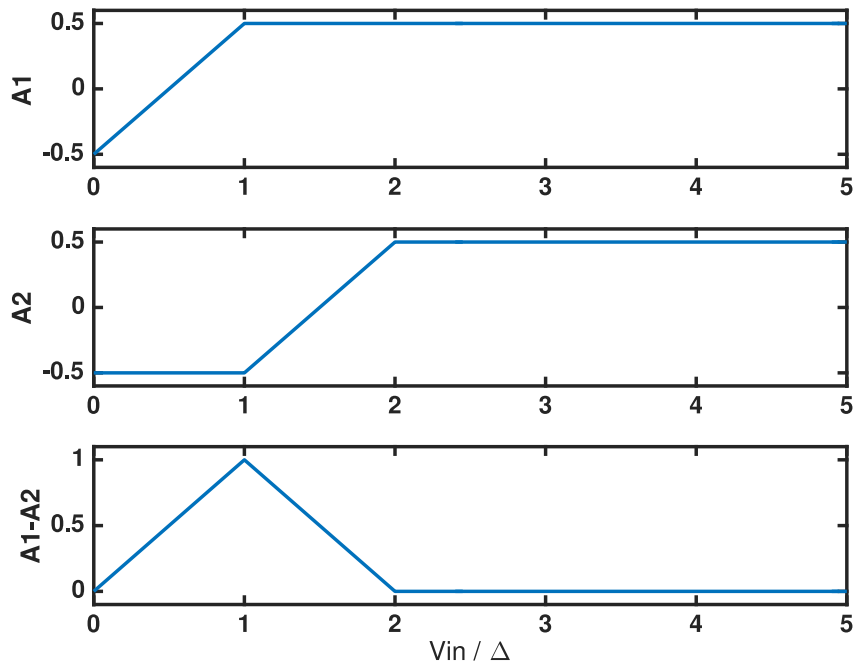
- Significantly fewer comparators than flash $\sim 2^{B/2+1}$
- Reduced input capacitance
- Nonidealities in folder limit resolution to ~ 10 Bits

Folding

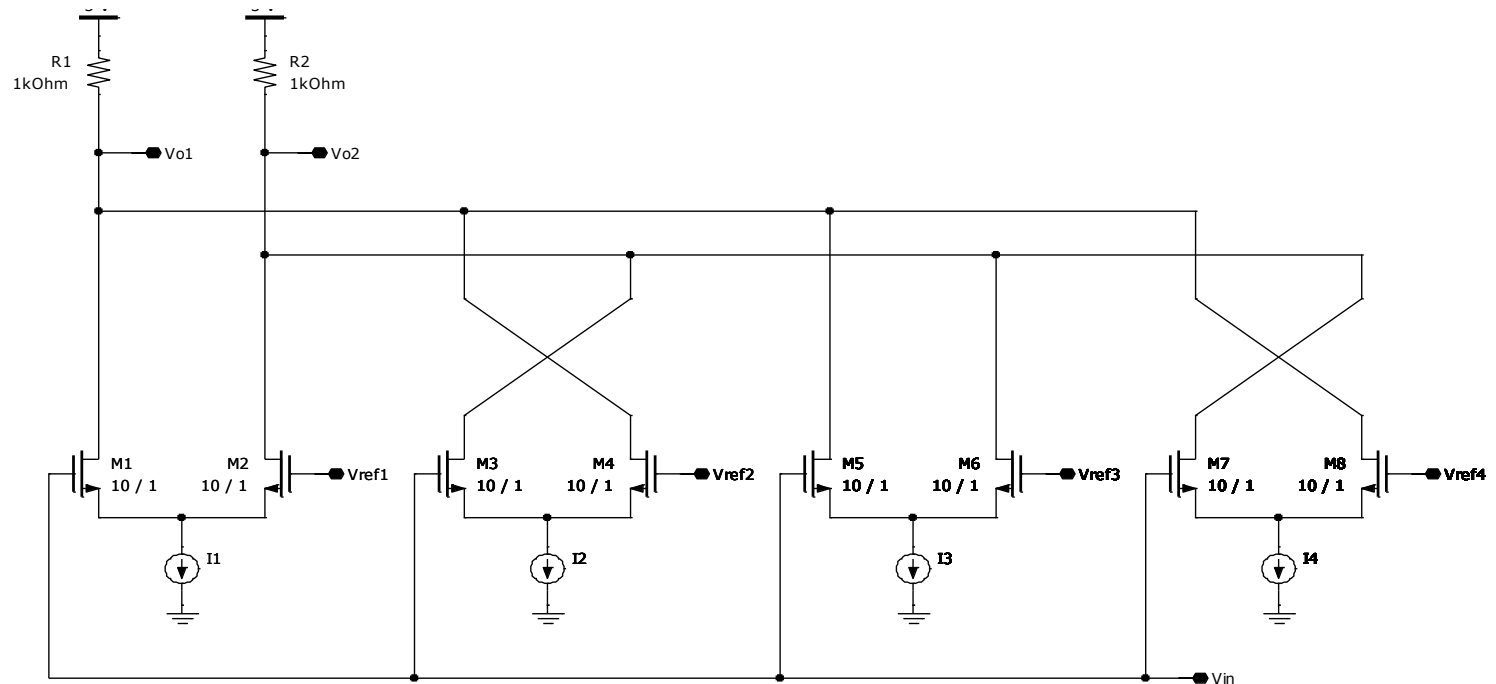
- Folder maps input to smaller range
- MSB ADC determines which fold input is in
- LSB ADC determines position within fold
- Logic circuit combines LSB and MSB results



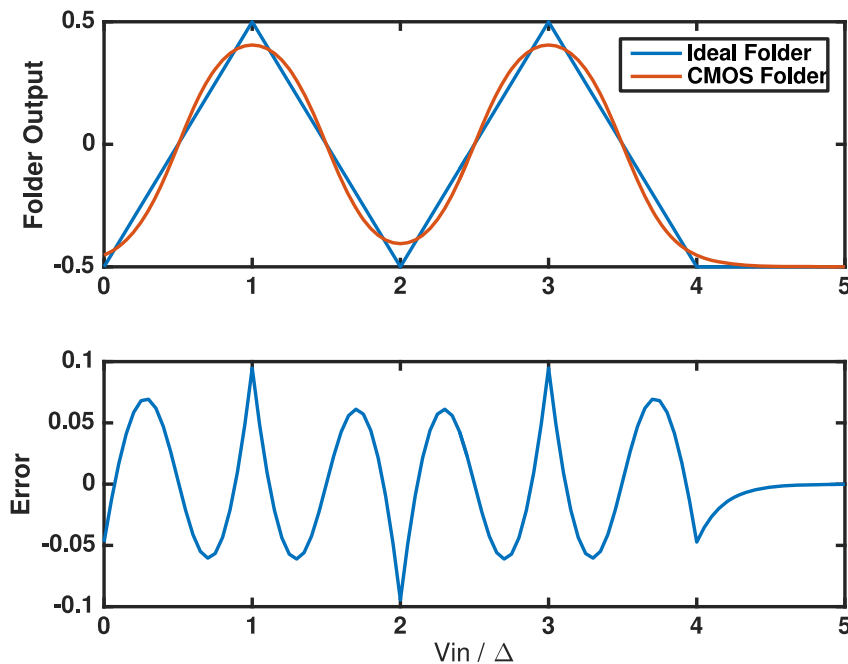
Generating Folds



Folding Circuit

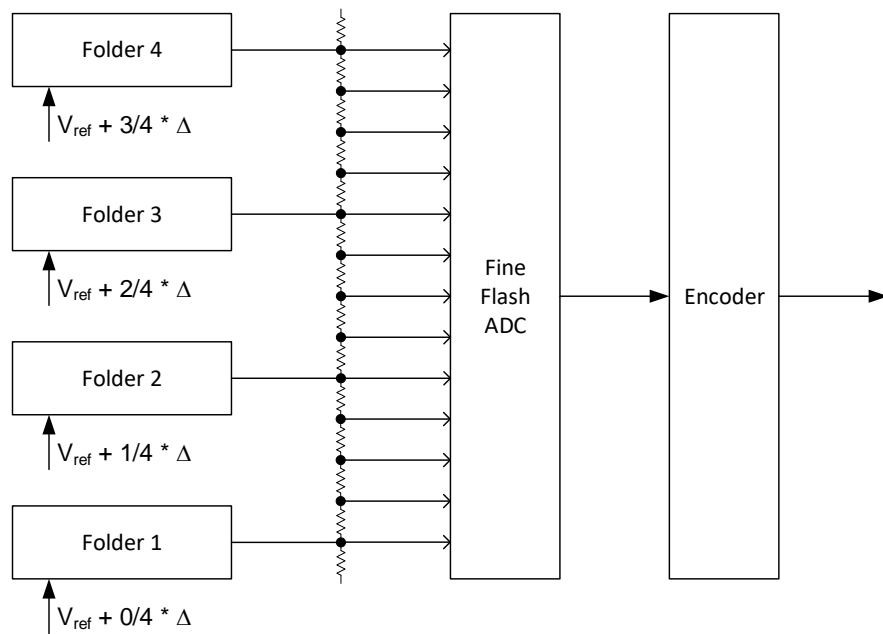


CMOS Folder Output



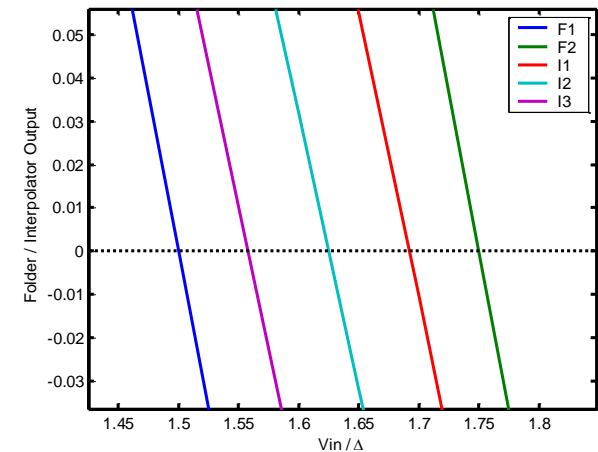
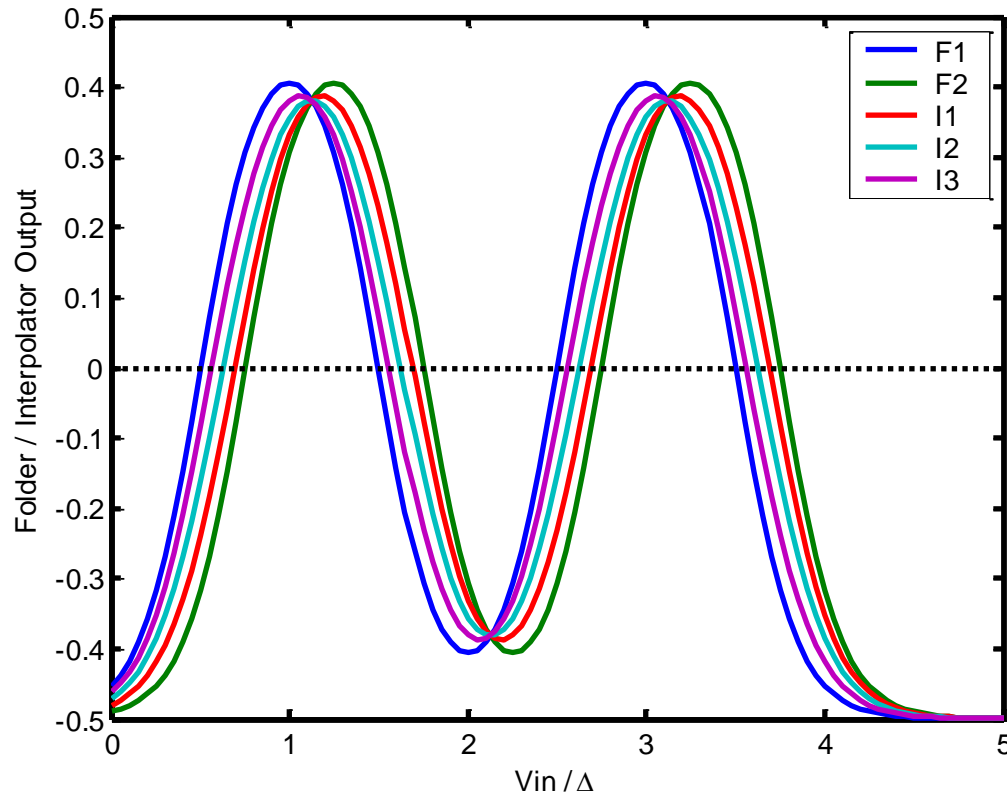
- Accurate only at zero-crossings
- Most folding ADCs do not actually use the folds, but only the zero-crossings!

Folding & Interpolation

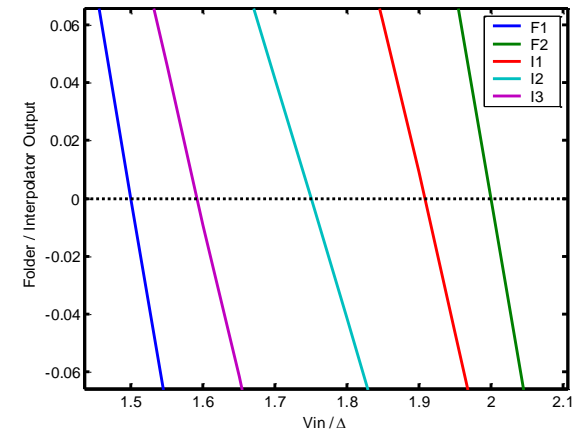
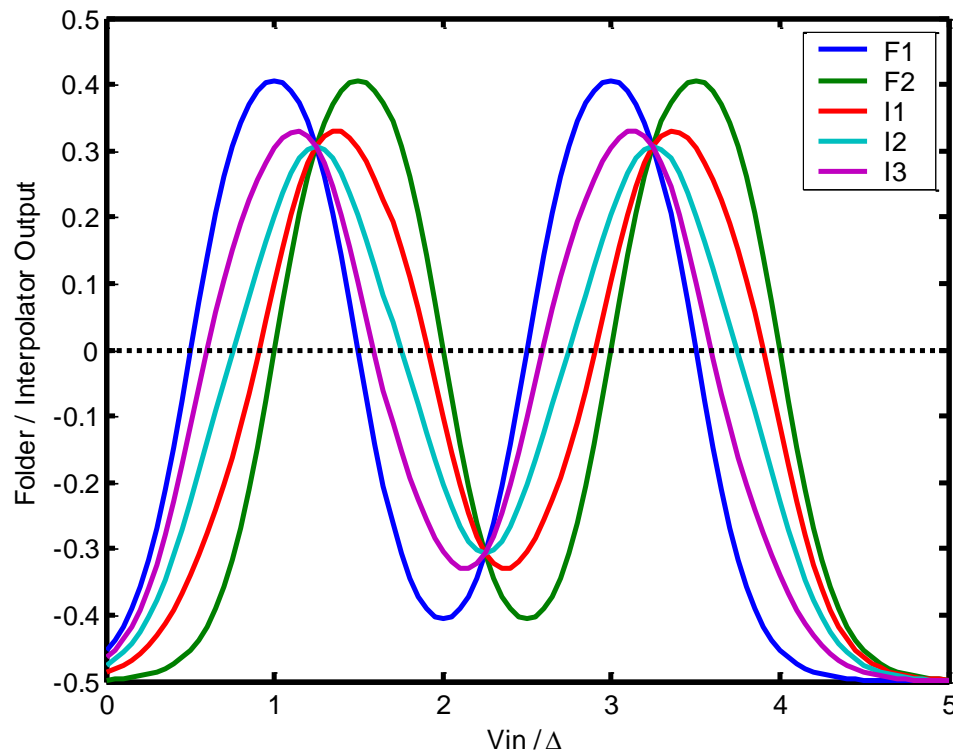


- Parallel folders
- Interpolate folder outputs

Folder / Interpolator Output



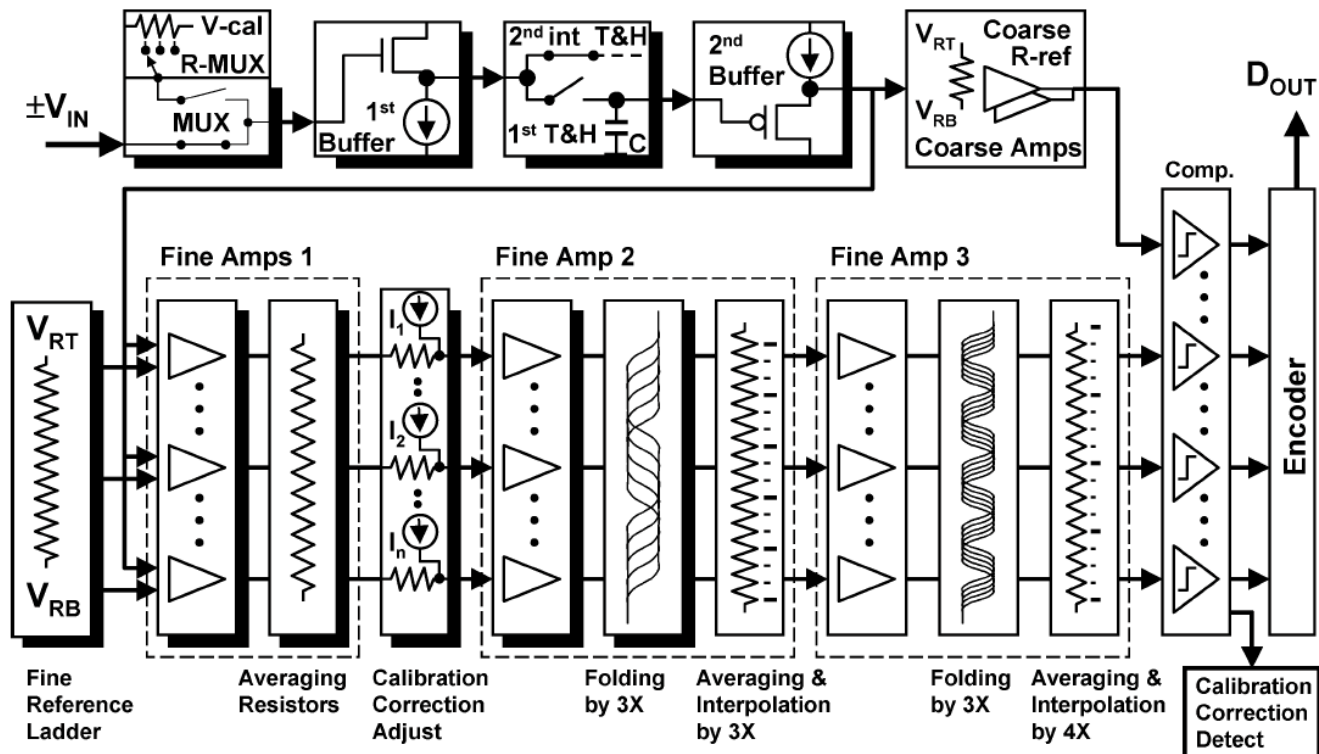
Folder / Interpolator Output



Interpolate only
between closely
spaced folds to avoid
nonlinear distortion

Folding and Interpolation ADC Example

R. C. Taft et al., "A 1.8-V 1.6-GSample/s 8-b self-calibrating folding ADC with 7.26 ENOB at Nyquist frequency," *IEEE Journal of Solid-State Circuits*, vol. 39, no. 12, pp. 2107–2115, Dec. 2004



Each folding stage:

- 9 x 3 diff pairs
- 3x folding
- 9 outputs

9x overall folding

9x reduction # comp

Folding and Interpolationg ADC Example

TABLE I
PERFORMANCE SUMMARY AT 1.6 GS/S FOR A SINGLE ADC

	$F_{IN} = 97.77 \text{ MHz}$	$F_{IN} = 797.77 \text{ MHz (Nyquist)}$
Sample Rate, F_S	1.6 GS/s	
Resolution	8 bits	
Max DNL	$\pm 0.15 \text{ LSB}$	
Max INL	$\pm 0.35 \text{ LSB}$	
SNR	48 dB	46 dB
SFDR	61 dB	56 dB
THD	- 57 dB	- 57 dB
ENOBs	7.60	7.26
Interleave aperture offset	< 0.35 ps @ $F_S = 1 \text{ GS/s}$ & $F_{IN} = 1.5 \text{ GHz}$	
Input (-3 dB) Bandwidth	> 1.75 GHz	
Resolution (-0.5 ENOB) Bandwidth	1.0 GHz	
Input Range	$\pm 400 \text{ mV differential}$	
Input Capacitance	1.8 pF (to gnd, w/o package)	
Input Termination	50 Ω (100 Ω differential)	
Single Supply	1.8 V	
Analog (DC) Current	245 mA	
Switching (AC) Current	185 mA	
LVDS Output Drivers	90 mA	
ADC Core Power (w/o outputs)	774 mW	
ADC core area	3.6 mm ²	
ADC die area	16 mm ² (for dual ADC, pad limited)	
Package	128-pin EPQFP	
Technology	0.18 μm CMOS (1-poly, 5-metal) No capacitor module nor dual-gate process	

R. C. Taft et al., “A 1.8-V 1.6-GSample/s 8-b self-calibrating folding ADC with 7.26 ENOB at Nyquist frequency,” *IEEE Journal of Solid-State Circuits*, vol. 39, no. 12, pp. 2107–2115, Dec. 2004

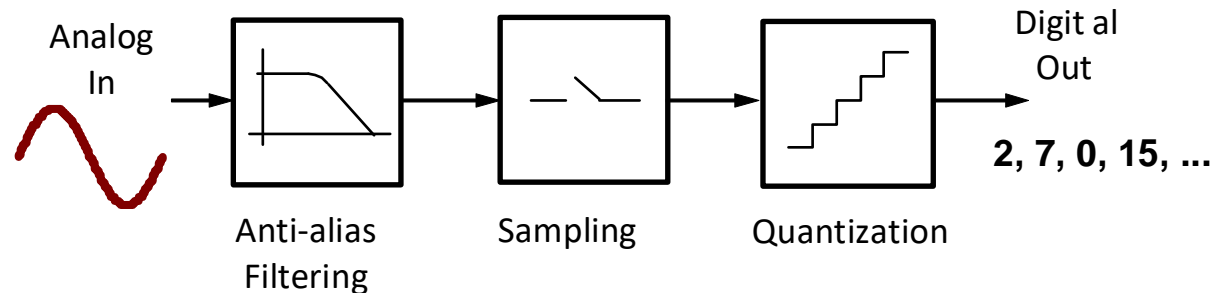
EE 240C

Analog-Digital Interface Integrated Circuits

Track & Hold Amplifier

Recap

A/D Conversion

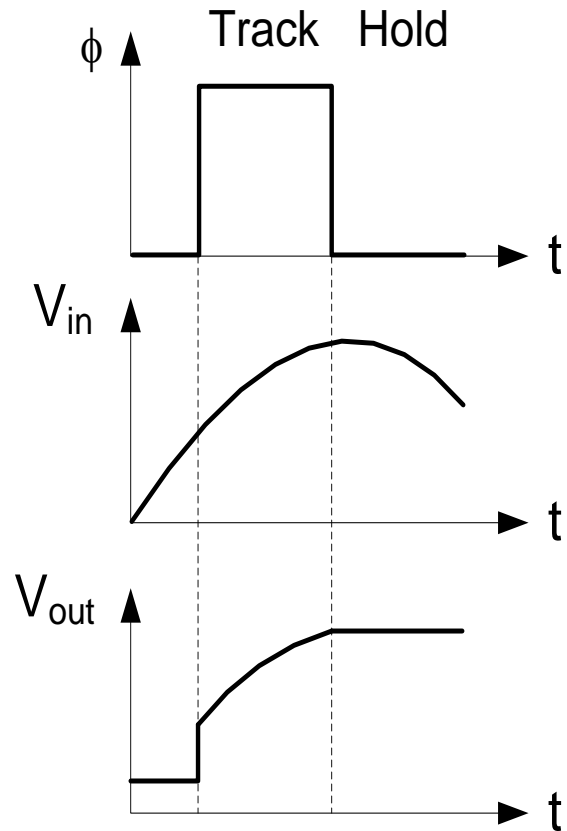
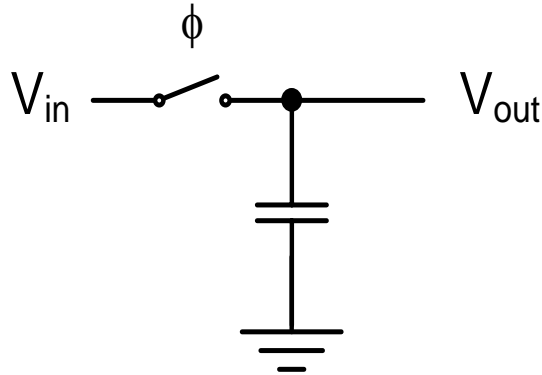


- How to build circuits that "sample"?
- Ideal Dirac sampling is impractical
 - Need a switch that opens, closes and acquires signal within an infinitely small time
- Practical solution
 - "Track & hold"
 - Customary to liberally use the term "SHA" = Sample & Hold, although the function is different

Outline

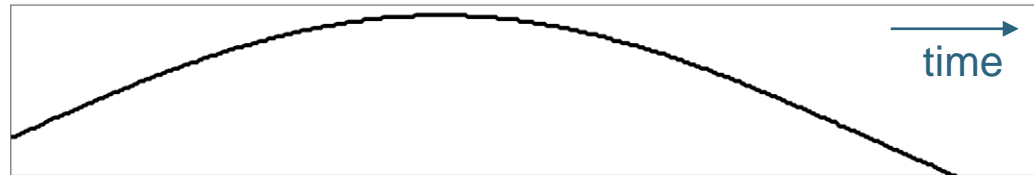
- Elementary track-and-hold circuit and its nonidealities
- First order improvements to elementary track-and-hold
- Advanced techniques
 - Clock bootstrapping
 - Bottom plate sampling
- Settling and noise analysis in charge-redistribution track-and-hold circuit
- Noise simulation example

Ideal Track-and-Hold Circuit

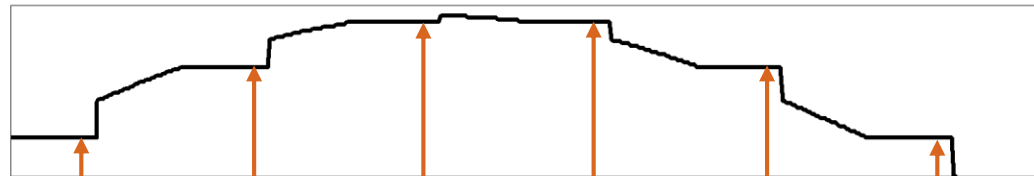


Signal Nomenclature

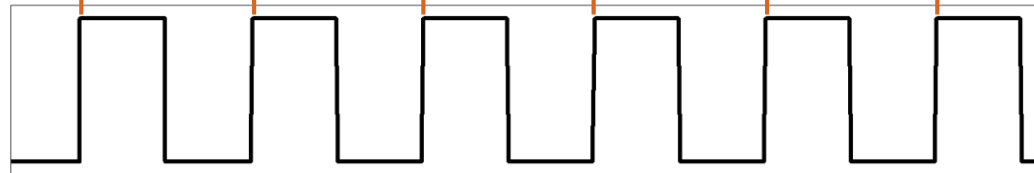
Continuous Time Signal



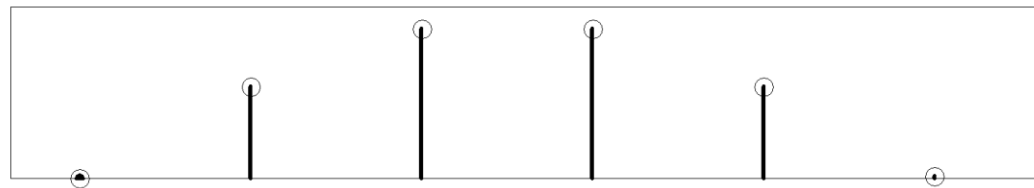
T/H Signal
("Sampled Data Signal")



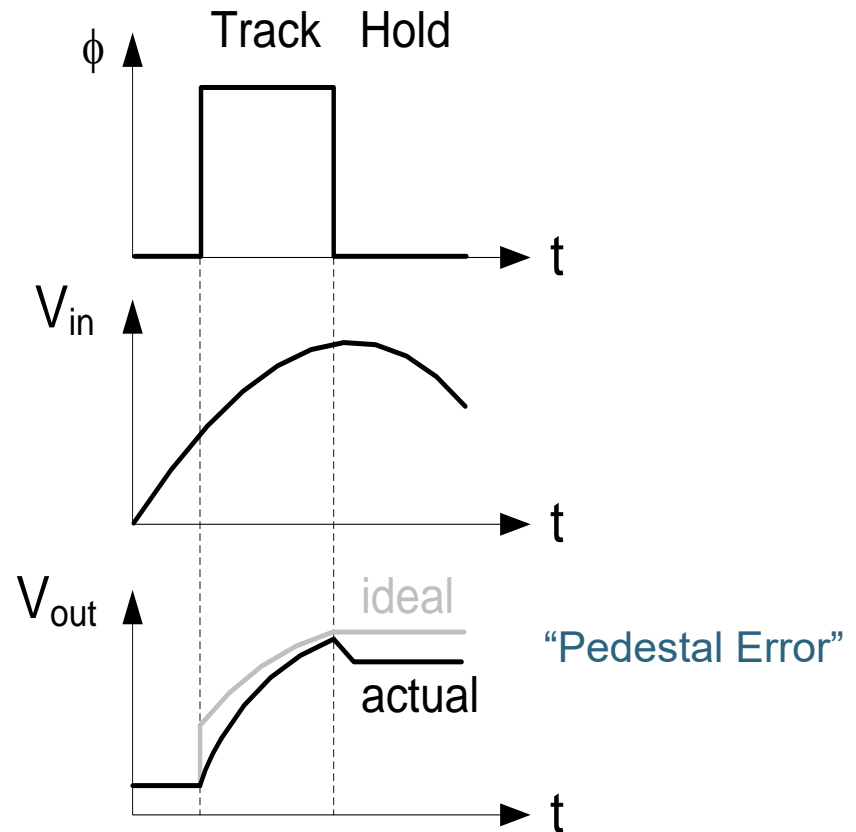
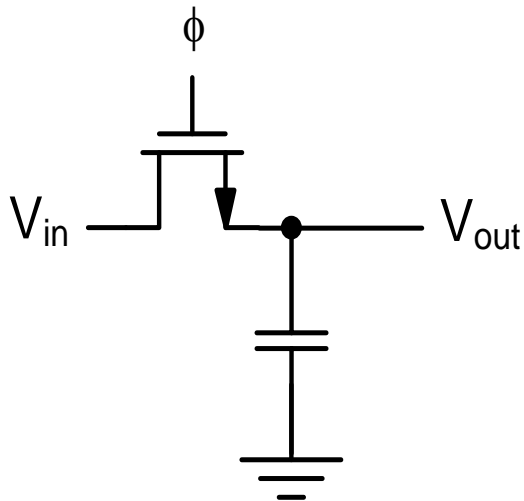
Clock



Discrete Time Signal



Circuit with MOS Switch



Nonidealities

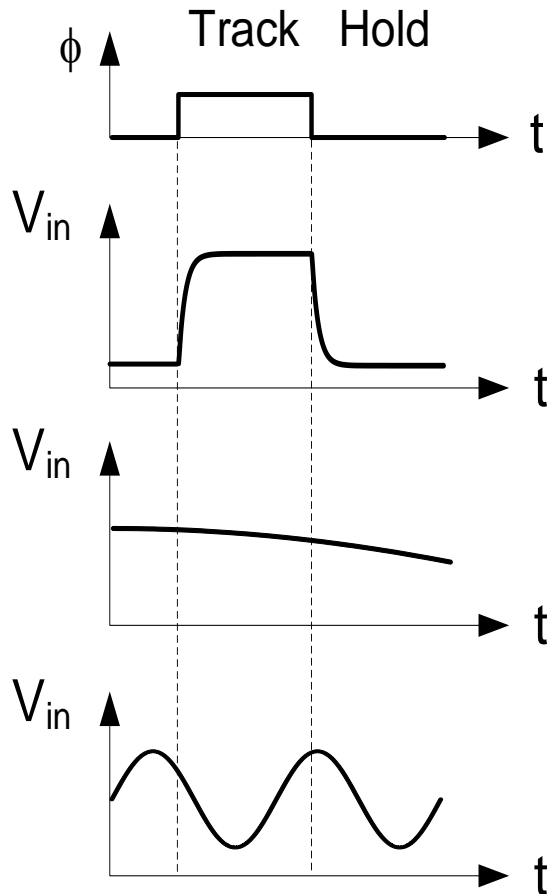
- Finite acquisition time
- Thermal noise
- Clock jitter
- Signal dependent hold instant
- Tracking nonlinearity
- Hold mode feedthrough and leakage
- Charge injection and clock feedthrough

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Track & Hold Amplifier Acquisition Time

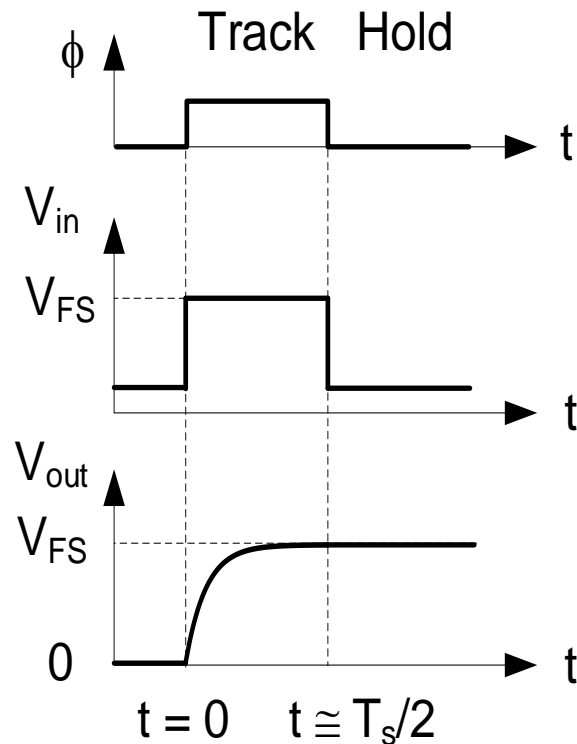
Finite Acquisition Time



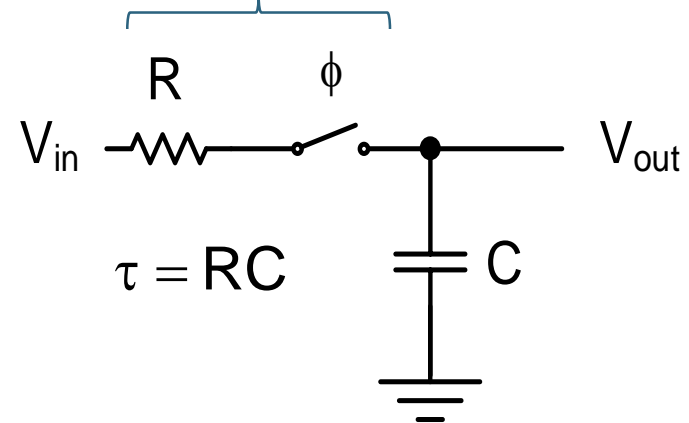
- Consider various input signal scenarios
1. Input is a sampled data signal, i.e. the output of another switched capacitor stage
 2. Input is a slowly varying continuous time signal, e.g. the input of an oversampling ADC
 3. Input is a rapidly varying continuous time signal, e.g. the input of a Nyquist or sub-sampling ADC

Finite Acquisition Time – Case 1

- For simplicity, neglect finite rise time of the input signal
- Consider worst case – the output is required to settle from 0 to the full-scale voltage of the system (V_{FS})



First order MOS switch model



$$\Rightarrow V_{out}(t) = V_{FS}(1 - e^{-t/\tau})$$

Finite Acquisition Time – Case 1

$$V_{\text{out,err}}\left(\frac{T_s}{2}\right) = -V_{\text{FS}}e^{-\frac{T_s}{2}/\tau} = -V_{\text{FS}}e^{-N}$$

- Typically think about settling error in terms of the number of settling time constants (N) required for ½ LSB settling in a B-bit system

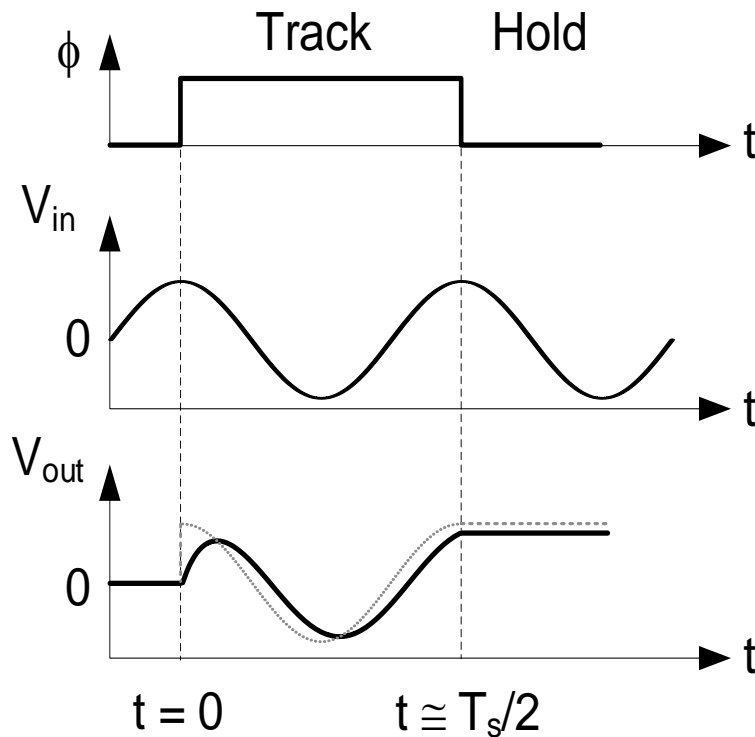
$$|-V_{\text{FS}}e^{-N}| \leq \frac{1}{2} \frac{V_{\text{FS}}}{2^B}$$

$$N = \frac{T_s/2}{\tau} \geq \ln(2 \cdot 2^B)$$

B	N
6	>4.9
10	>7.6
14	>10.4
18	>13.2

Finite Acquisition Time – Case 2 & 3

- Consider a sinusoidal input around “0”, and “0” also as the initial condition for V_{out} (for notational simplicity)



$$V_{\text{in}}(t) = A \cos(\omega t + \phi)$$

$$V_{\text{out}}(t) = \underbrace{-\frac{A \cos(\phi - \theta)}{\sqrt{1 + \omega^2 \tau^2}} e^{-\frac{t}{\tau}}}_{\text{initial transient}} + \underbrace{\frac{A \cos(\omega t + \phi - \theta)}{\sqrt{1 + \omega^2 \tau^2}}}_{\text{steady-state response}}$$

$$\theta = \text{atan}(\omega \tau)$$

Finite Acquisition Time – Case 2 & 3

- At $t=T_s/2$, the error in the held signal consists of two parts
- Residual error due to initial exponentially decaying initial transient term
 - In order to minimize this error, we need to choose N appropriately, as calculated for the step input scenario
- Error due to magnitude attenuation and phase shift in the steady state term
 - This error depends only on the RC time constant and the input frequency; it cannot be reduced by extending the length of the track phase
 - How significant is the error due to the steady-state term?

Finite Acquisition Time – Case 2 & 3

- As an example, let's compute the percent amplitude error for the N values derived previously (½ LSB, B-bit settling to a step)

$$A_{\text{err}} = \left| \frac{\frac{A}{\sqrt{1 + (\omega\tau)^2}} - A}{A} \right| = 1 - \frac{1}{\sqrt{1 + (\omega\tau)^2}} = 1 - \frac{1}{\sqrt{1 + \left(2\pi f_{\text{in}} \frac{T_s/2}{N}\right)^2}} = 1 - \frac{1}{\sqrt{1 + \left(\frac{\pi f_{\text{in}}}{N f_s}\right)^2}}$$

B	N	$A_{\text{err}} (f_{\text{in}} = f_s/20)$	$A_{\text{err}} (f_{\text{in}} = f_s/2)$
6	4.9	0.052%	4.9%
10	7.6	0.021%	2.1%
14	10.4	0.011%	1.1%
18	13.2	0.007%	0.7%

Summary – Finite Acquisition Time

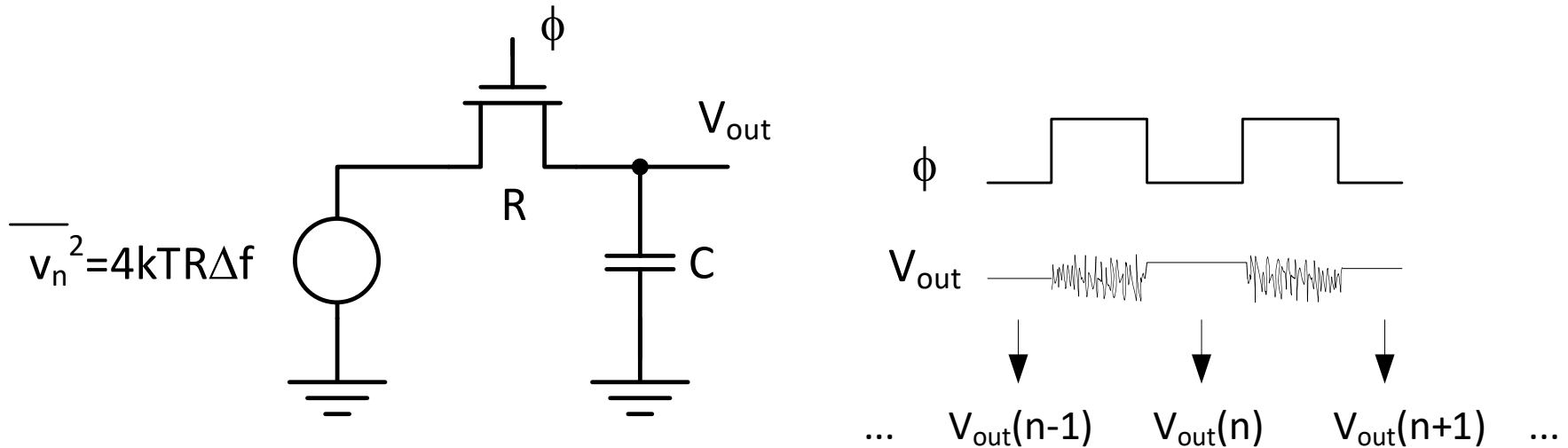
- Precise settling to an input step is accomplished within 5...13 RC time constants (depending on precision)
- Precise tracking of a high-frequency continuous time input signal tends to impose more stringent requirements
 - Number to remember: ~1% attenuation error at Nyquist ($f_{in}=f_s/2$) for $N \sim 10$
- In applications where attenuation is tolerable, the RC time constant requirements then tend to follow from the distortion specs
 - The larger the attenuation, the larger the instantaneous voltage drop across the (weakly nonlinear) MOSFET → undesired harmonics

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Track & Hold Amplifier – Noise

Thermal Noise (1)



- Questions

- What is the noise variance of the V_{out} samples in hold mode?
- What is the spectrum of the discrete time sequence representing these samples?
 - Nearly white, provided that the number of settling time constants (N) is large

Thermal Noise (2)

- Sample values $V_{out}(n)$ correspond to instantaneous values of the track mode noise process
- From Parseval's theorem, we know that the time domain power (or variance) of this process is equal to its power spectral density integrated over all frequencies
 - Further, given that the process is ergodic, this number must also be equal to the "ensemble" variance, i.e. the variance of a sample taken at a particular time

$$\frac{\overline{v_{out}^2}}{\Delta f} = 4kTR \cdot \left| \frac{1}{1 + sRC} \right|^2$$

$$\text{var}[V_{out}(n)] = \overline{v_{out,tot}^2} = \int_0^{\infty} 4kTR \cdot \left| \frac{1}{1 + j2\pi f \cdot RC} \right|^2 df = \frac{kT}{C}$$

Alternative Derivation

- The equipartition theorem says that each “degree of freedom” (typically a quadratic energy variable) of a system in thermal equilibrium holds an average energy of $kT/2$
- In our system, the degree of freedom is the energy stored on the capacitor

$$\overline{\frac{1}{2} C v_{\text{out}}^2} = \frac{1}{2} kT$$

$$\overline{v_{\text{out}}^2} = \frac{kT}{C}$$

Implications of kT/C Noise

- Example: suppose we make the kT/C noise equal to the quantization noise of a B-bit ADC

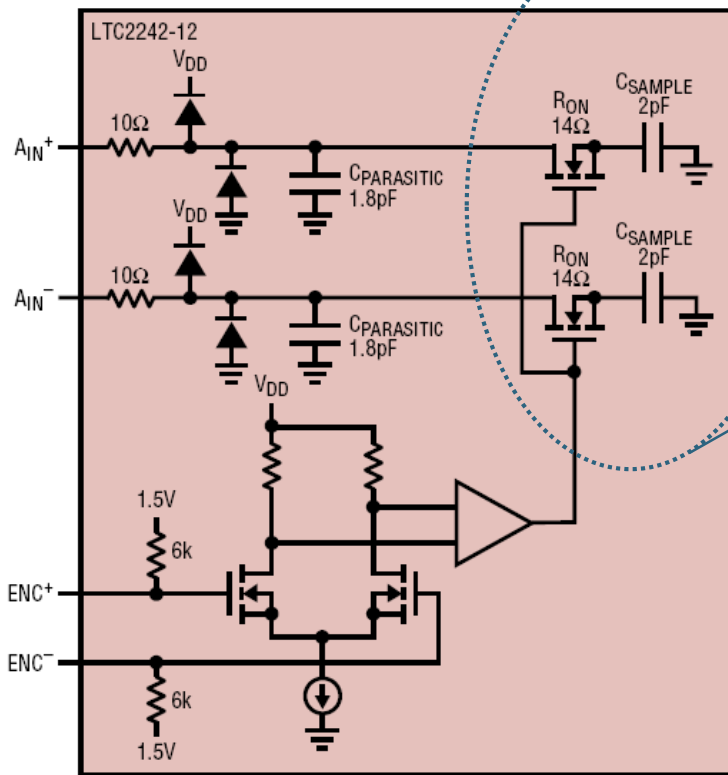
$$\frac{kT}{C} = \frac{\Delta^2}{12}, \quad \Delta = \frac{V_{FS}}{2^B} \Rightarrow C = 12kT \left(\frac{2^B}{V_{FS}} \right)^2$$

- For a given B, both C and R (via N on slide 19) are fully determined
- Example numbers for $V_{FS}=1V$ and $f_s=100MHz$:

B	C [pF]	R [Ω]
8	0.003	246,057
10	0.052	12,582
12	0.834	665
14	13.3	36
16	213	1.99
18	3,416	0.11

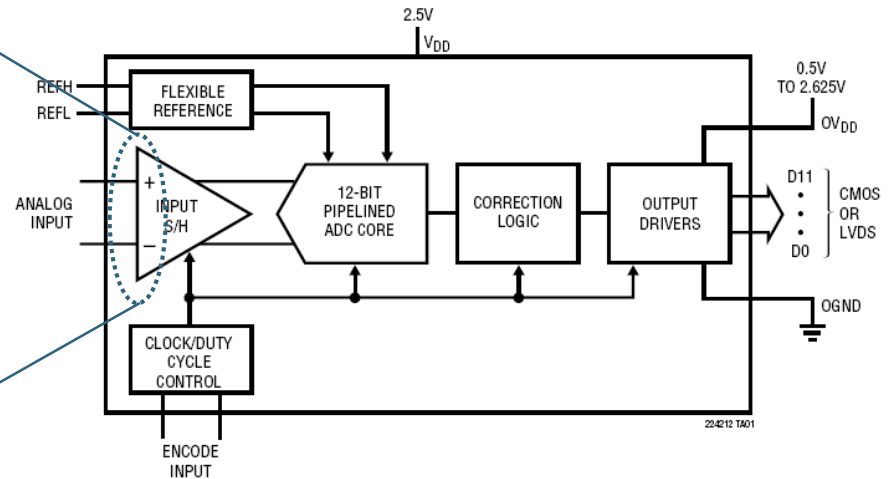
Commercial Example

Equivalent Input Circuit



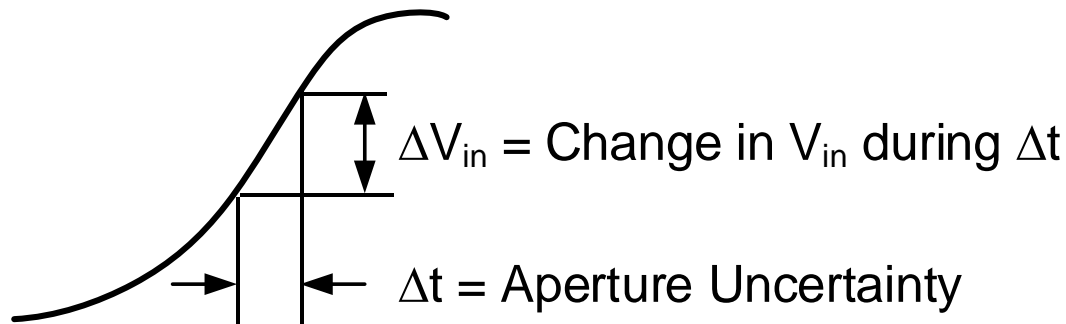
LTC2242-12

12-Bit, 250Msps ADC



Aperture Uncertainty

- In any sampling circuit, electronic noise causes random timing variations in the actual sampling clock edge
 - Adds "noise" to samples, especially if dV_{in}/dt is large



$$\Delta V_{in} \cong \frac{dV_{in}}{dt} \cdot \Delta t$$

- Analysis
 - Consider sine wave input signal
 - Assume Δt is random with zero mean and standard deviation σ_t

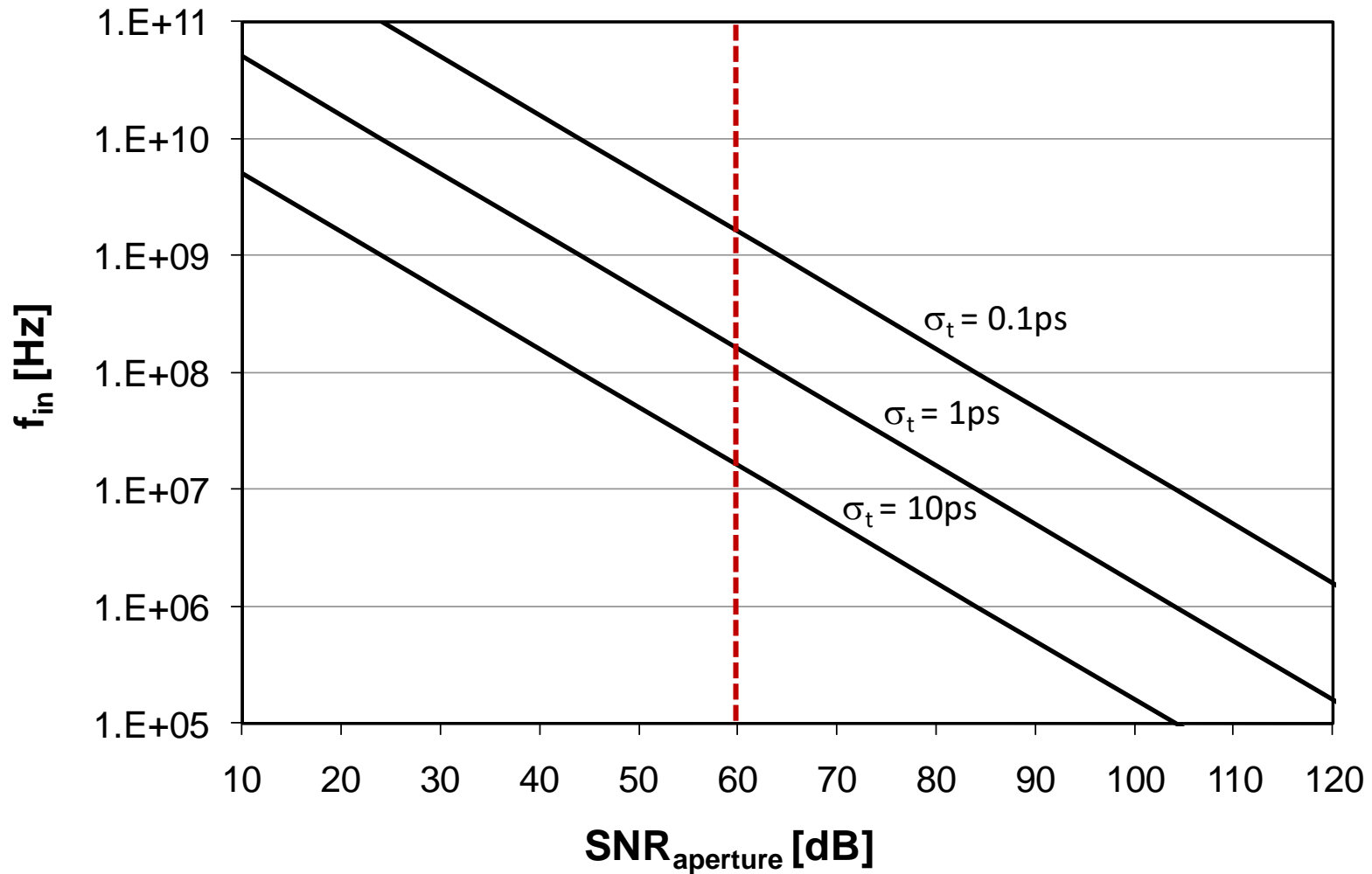
Analysis

$$\begin{aligned} E\{\Delta V_{\text{in}}^2\} &\cong E\left\{\left(\frac{dV_{\text{in}}}{dt}\right)^2 \cdot \Delta t^2\right\} = E\left\{\left(\frac{dV_{\text{in}}}{dt}\right)^2\right\} \cdot E\{\Delta t^2\} \\ &\cong E\left\{\left(\frac{d}{dt} A \cos[2\pi \cdot f_{\text{in}} \cdot t]\right)^2\right\} \cdot \sigma_t^2 \cong \frac{1}{2} (2\pi \cdot A \cdot f_{\text{in}})^2 \cdot \sigma_t^2 \end{aligned}$$

$$SNR_{\text{aperture}}[dB] \cong 10 \cdot \log \left[\frac{\frac{1}{2} A^2}{\frac{1}{2} (2\pi \cdot A \cdot f_{\text{in}} \cdot \sigma_t)^2} \right] = 20 \cdot \log \left[\frac{1}{2\pi \cdot f_{\text{in}} \cdot \sigma_t} \right]$$

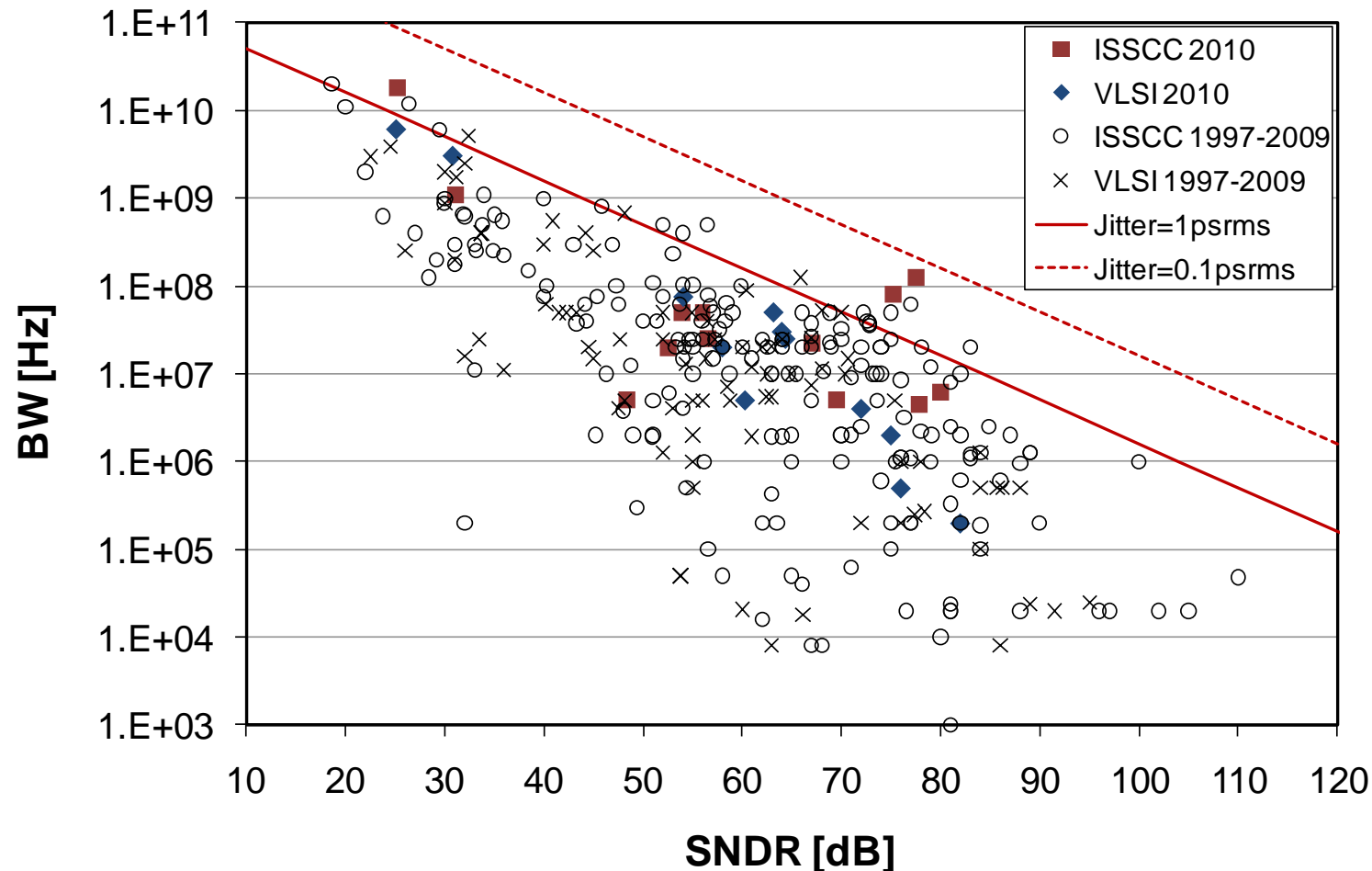
- For an input signal whose power is evenly distributed between $0 \dots f_s/2$, the above result improves by 4.8 dB
 - See e.g. [Da Dalt, TCAS1, 9/2002]

Result



ADC Performance Survey (ISSCC & VLSI 97-10)

Data: <http://www.stanford.edu/~murmunn/adcsurvey.html>



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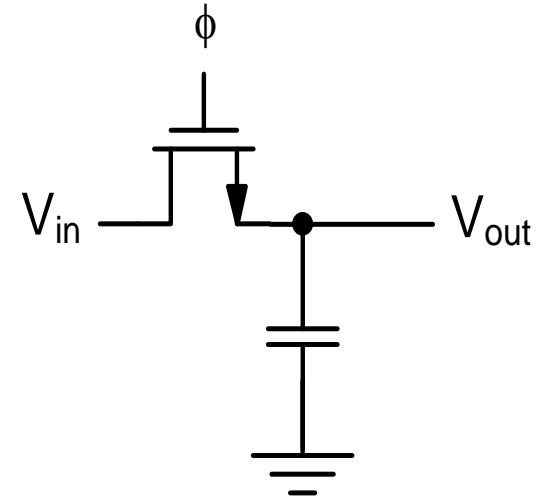
Track & Hold Amplifier – Linearity

Voltage Dependence of Switch

$$I_{D(\text{triode})} = \mu C_{ox} \frac{W}{L} \left(V_{GS} - V_t - \frac{V_{DS}}{2} \right) V_{DS}$$

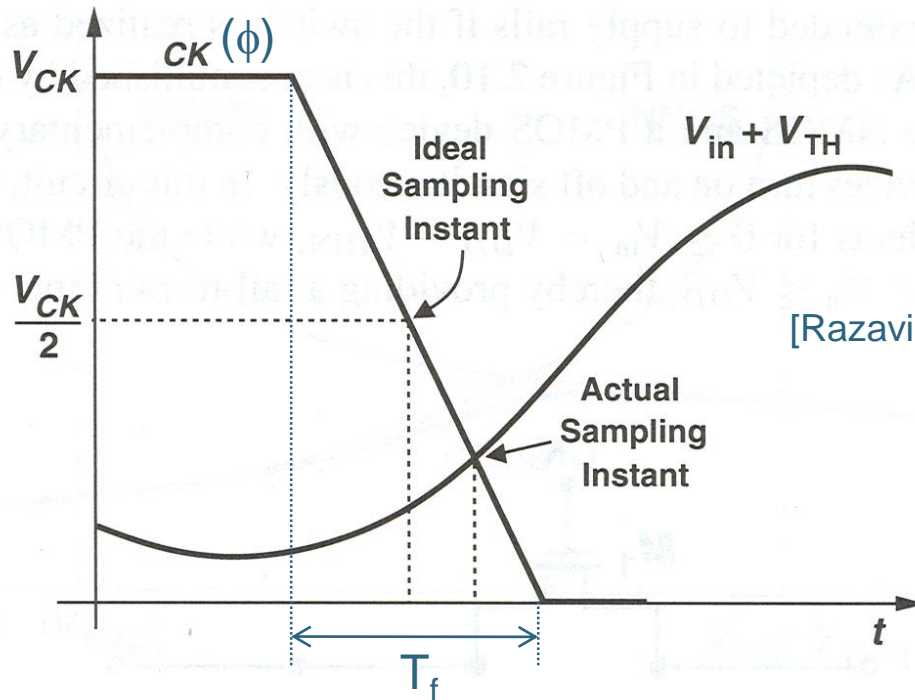
$$R_{ON} \cong \left[\frac{dI_{D(\text{triode})}}{dV_{DS}} \bigg|_{V_{DS} \rightarrow 0} \right]^{-1}$$

$$R_{ON} = \frac{1}{\mu C_{ox} \frac{W}{L} (\phi - V_{in} - V_t)}$$



- Two problems
 - Transistor turn off is signal dependent, occurs when $\phi = V_{in} + V_t$
 - R_{ON} is modulated by V_{in} (assuming e.g. $f = VDD = \text{const.}$)

Signal Dependent Sampling Instant (1)



[Razavi, Data Conversion System Design, p.17]

- Must make fall time of sampling clock (T_f) much faster than maximum dV_{in}/dt

Signal Dependent Sampling Instant (2)

- Distortion analysis result (see Yu, TCAS II, 2/1999]

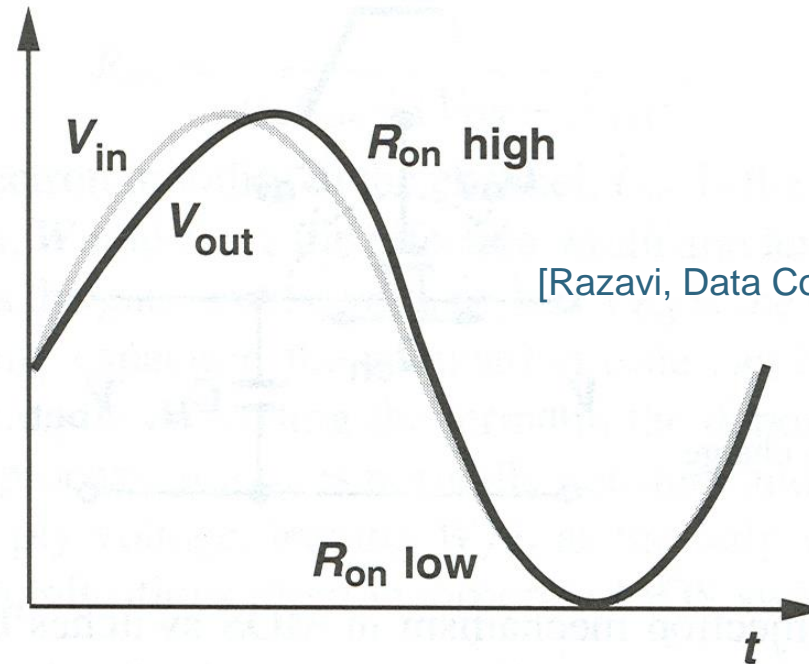
$$HD_3 = \frac{\text{Amplitude of third harmonic}}{\text{Amplitude of fundamental}} \\ \cong \frac{3}{8} \left(\frac{A}{V_{CK}} \omega T_f \right)^2$$

- Example:

$$V_{CK} = 1.8V, A = 0.5V, T_f = 100ps, \omega = 2\pi \cdot 100MHz$$

$$HD_3 \cong \frac{3}{8} \left(\frac{0.5}{1.8} \cdot 2\pi \cdot 100 \cdot 10^6 \cdot 100 \cdot 10^{-12} \right)^2 = -79dB$$

Track Mode Nonlinearity



[Razavi, Data Conversion System Design, p.16]

- Output tracks well when input voltage is low
 - Gets distorted when voltage is high due to increase in R_{ON}

Analysis

$$I_D \cong K(V_{GS} - V_t)V_{DS} - \frac{K}{2}V_{DS}^2$$
$$C \frac{dV_{out}}{dt} = K(\phi - V_{out} - V_t)(V_{in} - V_{out}) - \frac{K}{2}(V_{in} - V_{out})^2$$

- "All" we need to do is solve the above differential equation...
- Can use Volterra Series analysis
 - General method that allows us to calculate the frequency domain response of nonlinear circuits with memory
 - See e.g. EE 242B
- Luckily someone has already done this for us
 - See [Yu, TCAS II, 2/1999]

Result

$$HD_3 = \frac{\text{Amplitude of third harmonic}}{\text{Amplitude of fundamental}}$$
$$\cong \frac{1}{4} \left(\frac{A}{V_{GS} - V_t} \right)^2 \cdot \omega\tau = \frac{1}{4} \left(\frac{A}{V_{GS} - V_t} \right)^2 \frac{f_{in}}{f_s} \cdot \frac{\pi}{N}$$

- V_{GS} is the "quiescent point" value of the gate–source voltage; i.e. in the zero crossing of the sine input
- For low distortion
 - Make amplitude smaller than $V_{GS} - V_t$
 - Low swing \rightarrow bad for SNR
 - Make $1/\tau$ much larger than ω (input frequency)
 - Big switch \rightarrow may cost lots of power to drive, comes with large parasitic capacitances

Numerical Example

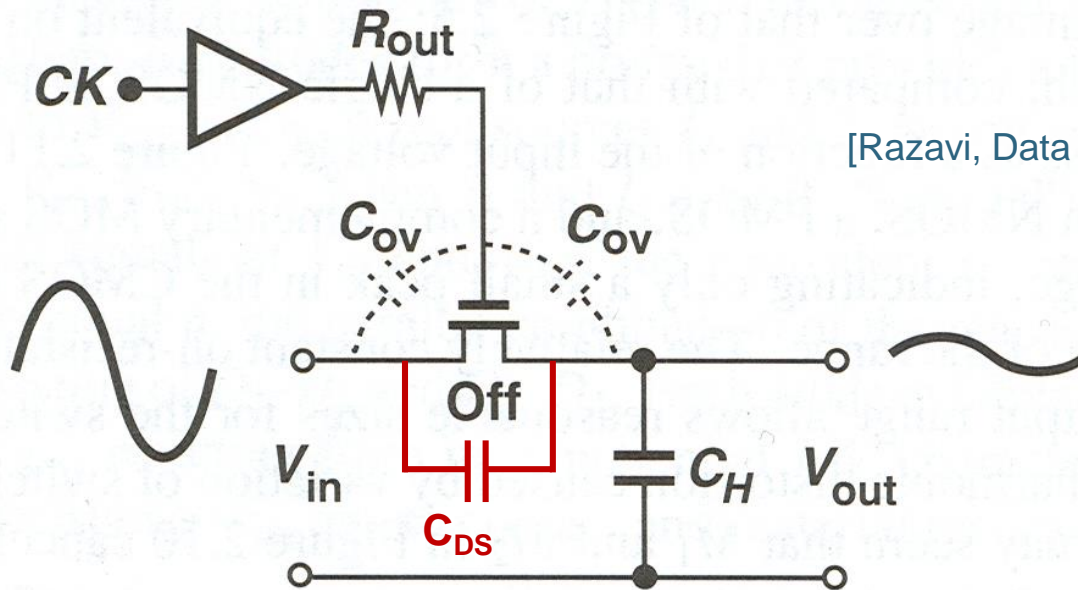
- Parameters

- $V_{DD} = V_{CK} = 1.8V$
- Signal is centered about $V_{DD}/2 = 0.9V$
- $V_{GS} - V_t = 1.8V - 0.9V - 0.45V = 0.45V$
- $A = 0.2V$
- $N = 0.5T_s/\tau = 10$
- $f_{in} = f_s/2$

$$HD_3 \cong \frac{1}{4} \left(\frac{0.2}{0.45} \right)^2 \frac{1}{2} \cdot \frac{\pi}{10} = -42dB$$

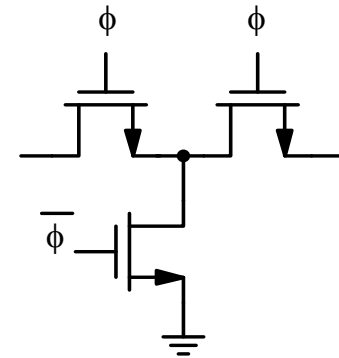
- Not all that great...

Hold Mode Feedthrough



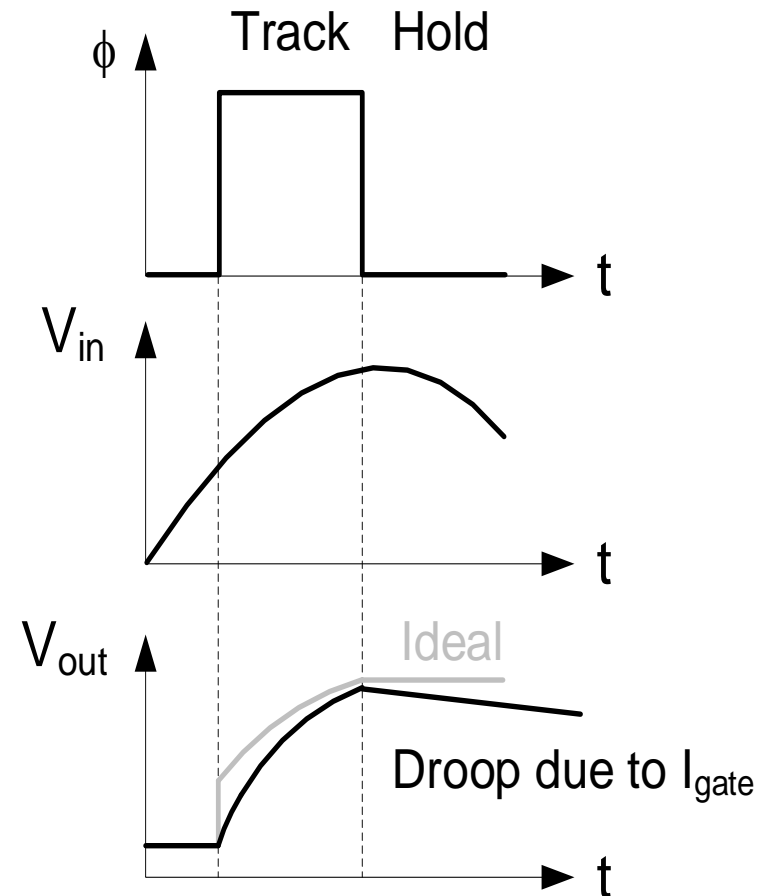
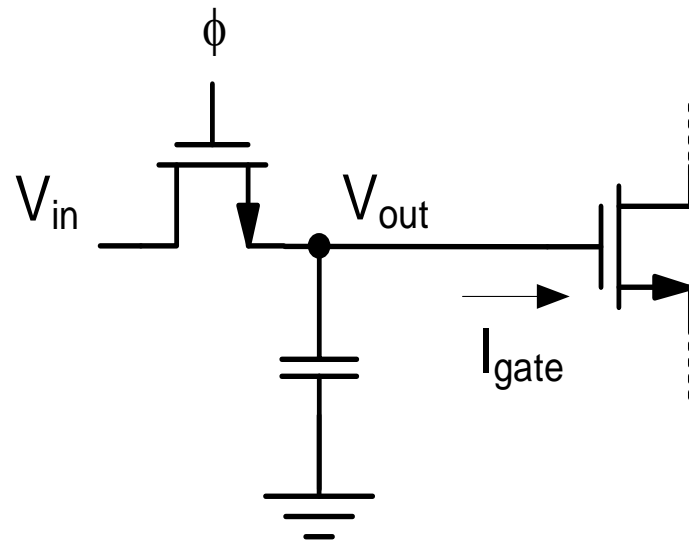
[Razavi, Data Conversion System Design, p.17]

- Want to make R_{out} as small as possible
- Consider using a “T-switch” when hold-mode feedthrough is a problem

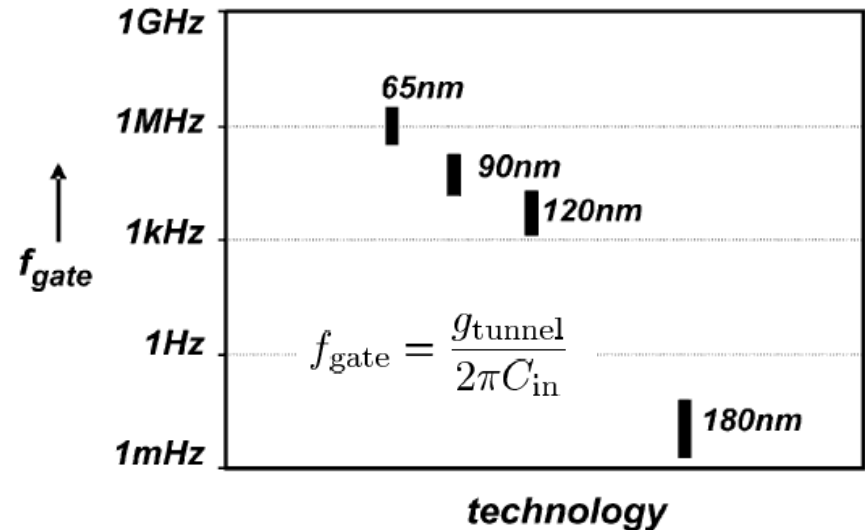
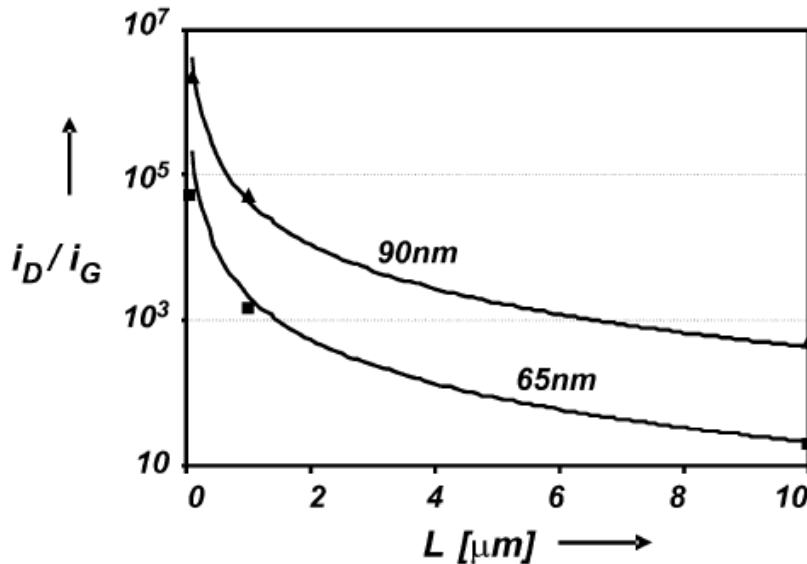


Hold Mode Leakage

- Example:



Gate Leakage Data



A. Annema, et al., "Analog circuits in ultra-deep-submicron CMOS," *IEEE J. Solid-State Circuits*, pp. 132-143, Jan. 2005.

$$\frac{dv_C}{dt} \approx -\gamma_{dv\,dt} \cdot f_{\text{gate}} \left[\frac{V}{s} \right] \quad \text{with } \gamma_{dv\,dt} \approx 1 \text{ V.}$$

- In 65nm CMOS, gate capacitance droop rate is $\sim 1\text{V/ms}$ (!)
- Issue is solved with high- k dielectrics in post-65nm technologies

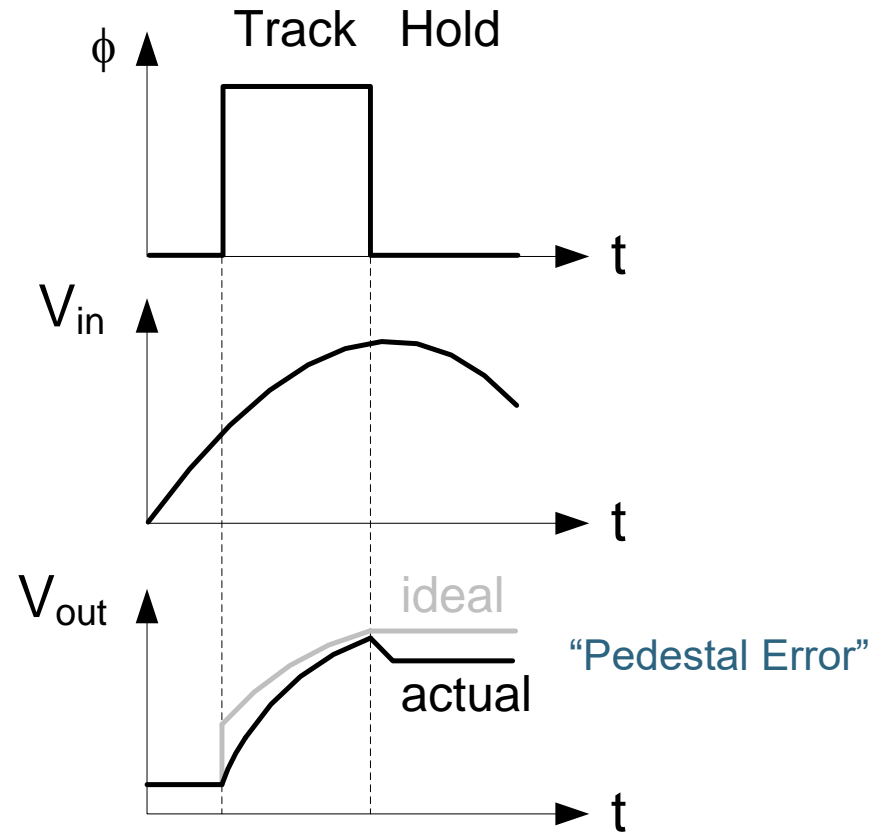
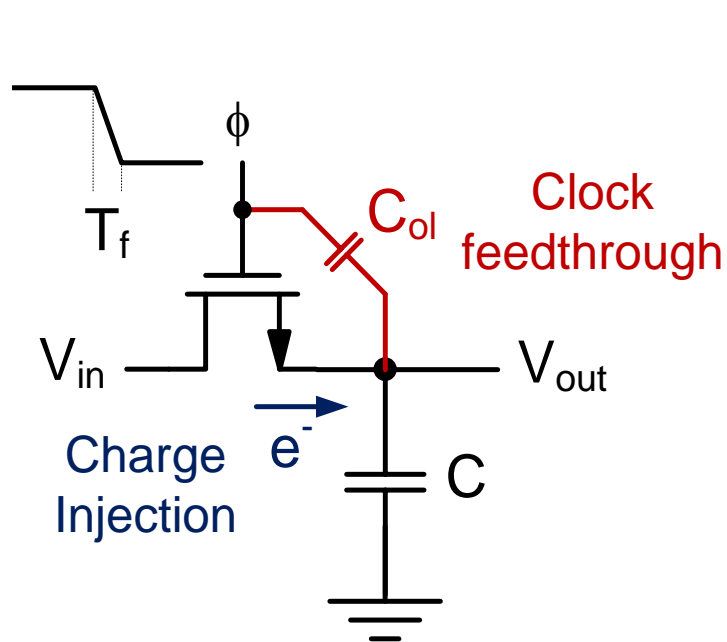
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Track & Hold Amplifier

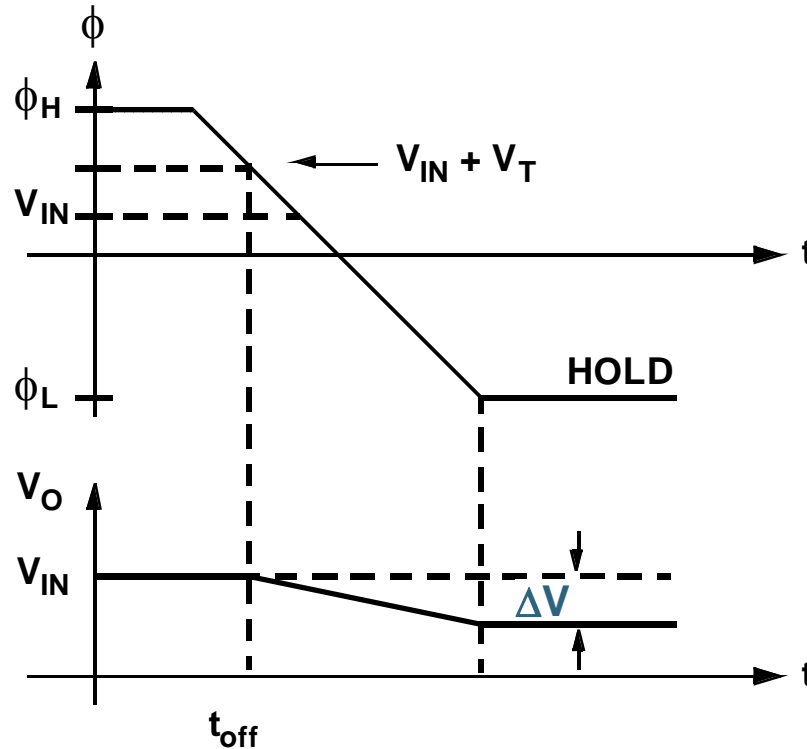
Switch Charge Injection

Charge Injection and Clock Feedthrough



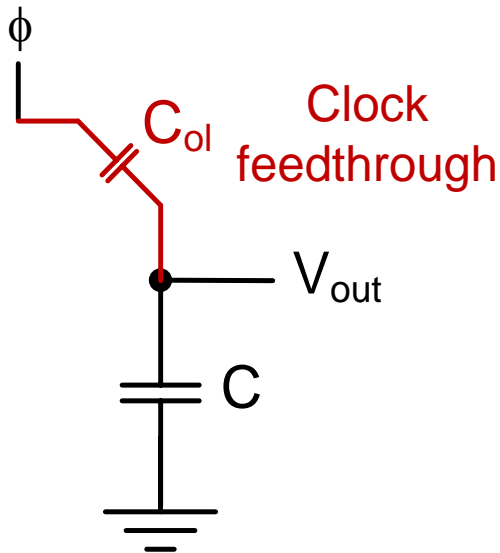
- Analyze two extreme cases
 - Very large T_f ("slow gating")
 - Very small T_f ("fast gating")

Slow Gating



- All channel charge has disappeared by t_{off} without introducing error; it is absorbed by the input source

Slow Gating Model for $t > t_{\text{off}}$



$$V_{\text{out}} = V_{\text{in}} - \Delta V_{\text{out}}$$

$$V_{\text{out}} = V_{\text{in}} - \frac{C_{\text{ol}}}{C_{\text{ol}} + C} (V_{\text{in}} + V_{\text{t}} - \phi_{\text{L}}) = V_{\text{in}} (1 + \varepsilon) + V_{\text{os}}$$

$$\varepsilon = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C}$$

Gain Error

$$V_{\text{os}} = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C} (V_{\text{t}} - \phi_{\text{L}})$$

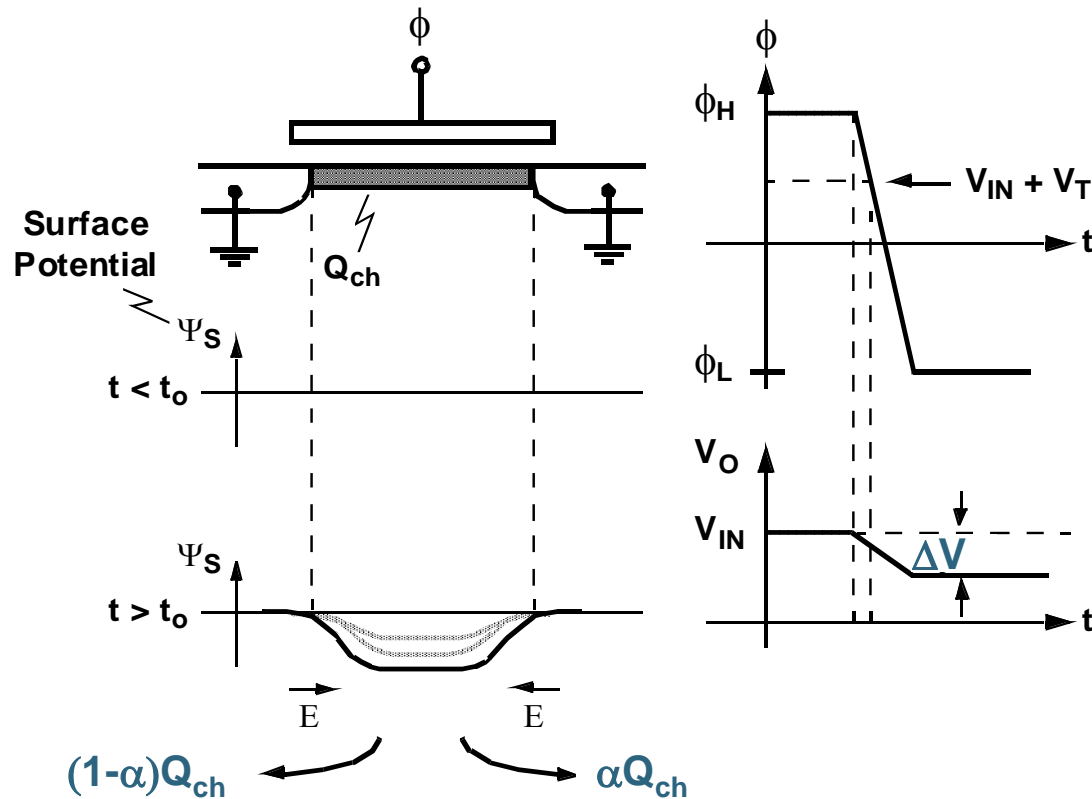
Offset Error

- Example: $C = 1\text{pF}$, $\phi_{\text{L}} = 0\text{V}$, $V_{\text{t}} = 0.45\text{V}$, $W = 20\mu\text{m}$, $C_{\text{ol}}' = 0.1\text{fF}/\mu\text{m}$, $C_{\text{ol}} = 2\text{fF}$

$$\varepsilon = -0.2\%$$

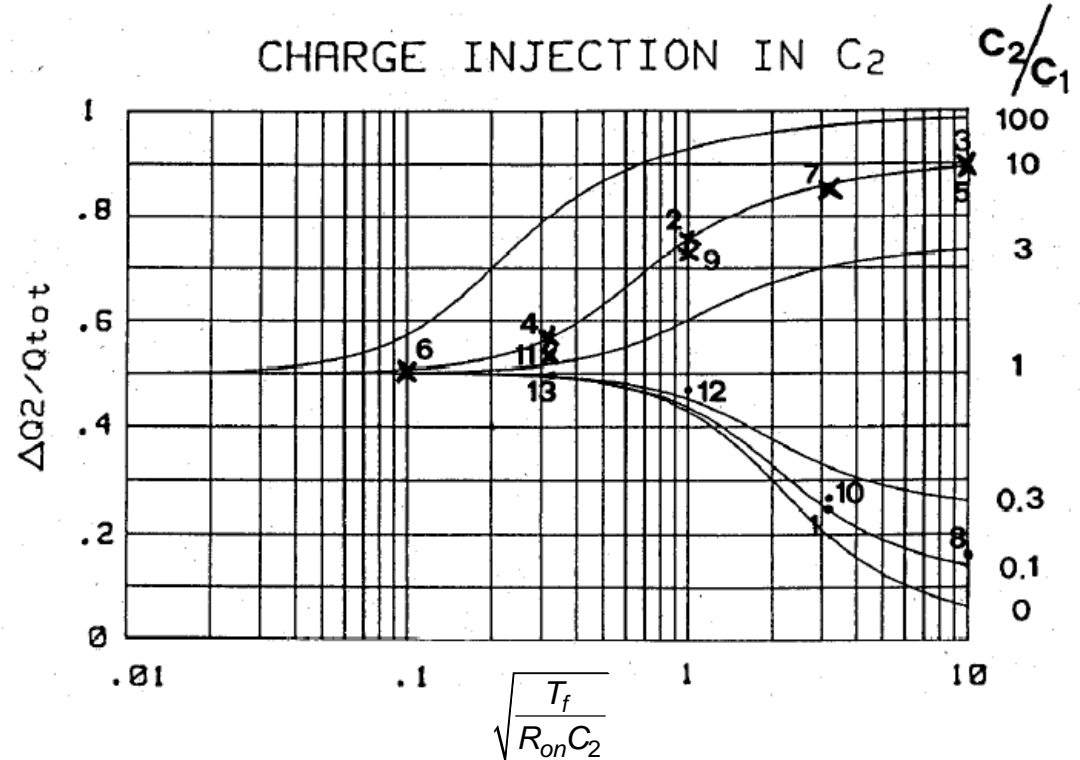
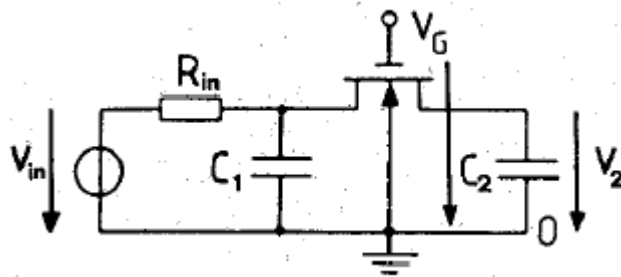
$$V_{\text{os}} = -0.9\text{mV}$$

Fast Gating



- Channel charge cannot change instantaneously
- Resulting surface potential decays via charge flow to source and drain
- Charge divides between source and drain depending on impedances loading these nodes

Charge Split Ratio Data



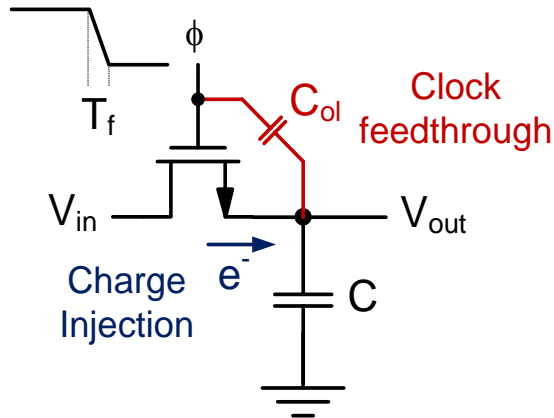
G. Wegmann et al., "Charge injection in analog MOS switches," IEEE J. Solid-State Circuits, pp. 1091-1097, June 1987.

Y. Ding and R. Harjani, "A universal analytic charge injection model," Proc. ISCAS, pp. 144-147, May 2000.

Interpretation

- $R_{on}C_2$ and T_f are usually comparable, or at least not more than an order of magnitude apart
 - This brings us into the range of 0.1...1 on the chart by Wegmann
- This means that the charge split will in practice have some dependence on the impedances seen on the two sides of the transistor
- Remember: Slightly more charge will go to the side with lower impedance

Fast Gating Model for $t > t_{\text{off}}$



$$V_{\text{out}} = V_{\text{in}} - \Delta V_{\text{out}} = V_{\text{in}} (1 + \varepsilon) + V_{\text{os}}$$

$$V_{\text{out}} = V_{\text{in}} - \frac{C_{\text{ol}}}{C_{\text{ol}} + C} (\phi_{\text{H}} - \phi_{\text{L}}) + \frac{1}{2} \frac{Q_{\text{ch}}}{C} \quad \text{Assuming 50/50 charge split}$$

$$Q_{\text{ch}} = -WLC_{\text{ox}} [\phi_{\text{H}} - V_{\text{in}} - V_{\text{t}}]$$

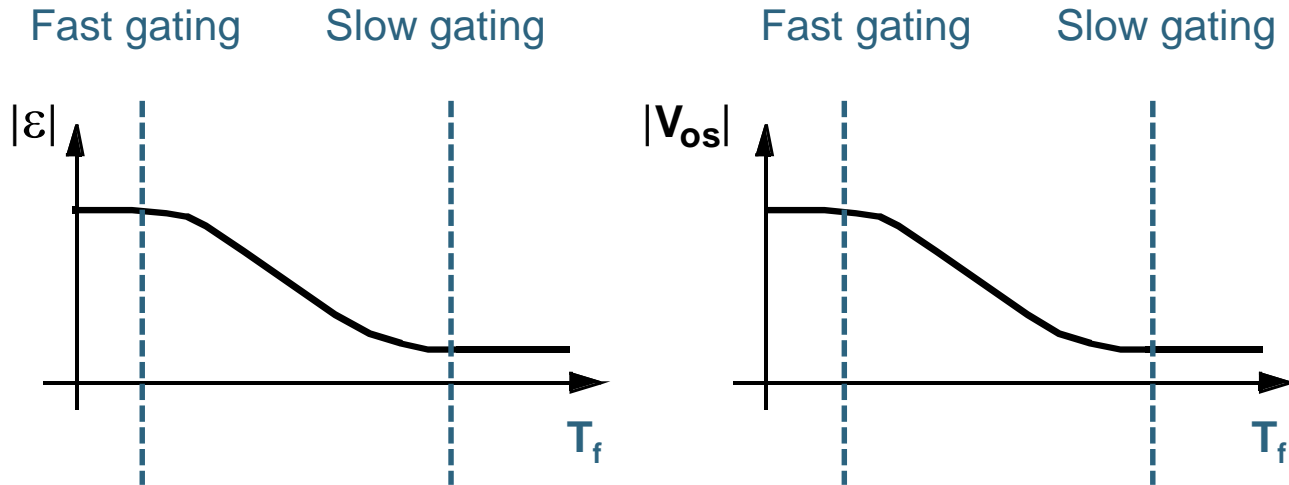
$$\varepsilon = \frac{1}{2} \frac{WLC_{\text{ox}}}{C} \quad V_{\text{os}} = -\frac{C_{\text{ol}}}{C_{\text{ol}} + C} (\phi_{\text{H}} - \phi_{\text{L}}) - \frac{1}{2} \frac{WLC_{\text{ox}}}{C} (\phi_{\text{H}} - V_{\text{t}})$$

- Example: $C=1\text{pF}$, $\phi_{\text{H}}-\phi_{\text{L}}=1.8\text{V}$, $V_{\text{t}}=0.45\text{V}$, $W=20\mu\text{m}$, $LC_{\text{ox}}=2\text{fF}/\mu\text{m}$, $C_{\text{ol}}'=0.1\text{fF}/\mu\text{m}$, $C_{\text{ol}}=2\text{fF}$

$$\varepsilon = +2\%$$

$$V_{\text{os}} = -30.6\text{mV}$$

Transition Fast/Slow Gating



- $|\epsilon|$ and $|V_{os}|$ decrease as the fall time of ϕ (T_f) increases and approach the limit case of slow gating
- Unfortunately, high-speed switched capacitor circuits tend to operate in fast gating regime

Impact of Technology Scaling

$$\left. \begin{aligned} \Delta V &\cong \frac{1}{2} \frac{Q_{ch}}{C} & \frac{1}{2f_s} = \frac{T_s}{2} = N \cdot RC \\ R &\cong \frac{1}{\mu C_{ox} \frac{W}{L} (V_{GS} - V_t)} = \frac{L^2}{\mu Q_{ch}} \end{aligned} \right\} \boxed{\frac{\Delta V}{f_s} \cong N \frac{L^2}{\mu}}$$

- Charge injection error to speed ratio benefits from shorter channels and increases in mobility (e.g. due to strain)